# MM3474 series application note

#### **Outline**

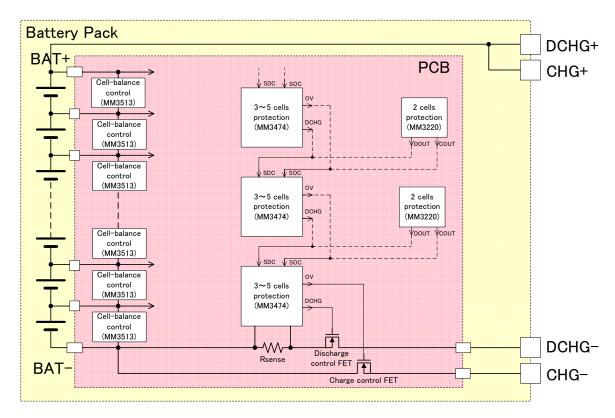
MM3474 series is an overcharge, overdischarge and overcurrent protection IC for a lithium-ion / lithium-polymer secondary battery. This supports 3 to 5 serial cells, and the number of cells can be switched over by inputting high / low signal to SEL terminal. MM3474 series can protect Lithium ion battery pack of 6-plus serial cells by connecting in cascade. This also provides the control terminals of output overdischarge detection (SDC) and output overcharge detection (SOC), which allows configuring an application with fewer external parts for 6 or more cells connected in series.

We provide many kinds of optional ICs of MM3474 series, which are customizable for the usage by selecting optional functions.

Low cost and small size configuration can be achieved when MM3474 series is combined with MM3220V series which is 2 cells protection IC and used for the applications of 6 cells or 7 cells, etc.

Cell balance control function can be added when MM3513 series which is cell balance control IC is used.

This application note is a reference material which describes representative examples of connection and cautions of designing for the applications which use MM3474 series, main characteristics and related products of MM3474 series. Please refer the data sheets for the details and specifications of this product.



lulti-cell protection circuit which uses MM3474 series and related products

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List of application circuit examples

Number of cells	Charge / discharg e route	Over discharge release method *1	Configuration of protect IC	Optional function *2 cell balance	Page
3cells	separate	Non Latch	3cells protection	-	P23
SCEIIS	common	Non Latch	3cells protection	-	P24
4cells	separate	Non Latch	4cells protection	-	P25
400113	common	Non Latch	4cells protection	-	P26
		Non Latch	5cells protection	-	P27
5cells	common	Non Latch	5cells protection	-	P28
	separate	Non Latch	5cells protection	0	P65
	separate	Non Latch	3cells protection+3cells protection	-	P29
6cells	separate	Latch	3cells protection+3cells protection	-	P30
ocens	separate	Non Latch	4cells protection+2cells protection	-	P57
	separate	Latch	4cells protection+2cells protection	-	P58
	separate	Non Latch	4cells protection+3cells protection	-	P31
7cells	separate	Latch	4cells protection+3cells protection	-	P32
/ cells	separate	Non Latch	5cells protection+2cells protection	-	P59
	separate	Latch	5cells protection+2cells protection	-	P60
Ocalla	separate	Non Latch	4cells protection+4cells protection	-	P33
8cells	separate	Latch	4cells protection+4cells protection	-	P34
Ocalla	separate	Non Latch	4cells protection+5cells protection	-	P35
9cells	separate	Latch	4cells protection+5cells protection	-	P36
	separate	Non Latch	5cells protection+5cells protection	-	P37
	common	Non Latch	5cells protection+5cells protection	-	P38
10cells	separate	Latch	5cells protection+5cells protection	-	P39
	common	Latch	5cells protection+5cells protection	-	P40
	separate	Non Latch		0	P66
	separate	Non Latch	4cells protection+4cells protection+4cells protection	-	P41
4011-	separate	Latch	4cells protection+4cells protection+4cells protection	-	P42
12cells	separate	Non Latch	5cells protection+5cells protection+2cells protection	-	P61
	separate		5cells protection+5cells protection+2cells protection	-	P62
40 = 11:	•	Non Latch		-	P43
13cells	separate		4cells protection+4cells protection+5cells protection	-	P44
146505		Non Latch		-	P45
14cells	separate		4cells protection+5cells protection+5cells protection	-	P46
			4cells protection+4cells protection+4cells protection	-	P47
40. "	separate	Latch	4cells protection+4cells protection+4cells protection	-	P48
16cells	-		4cells protection+5cells protection+5cells protection+	-	P63
	separate	Latch	4cells protection+5cells protection+5cells protection	-	P64

%1 Non Latch : Voltage release

#### 1. Function outline of MM3474 series

#### 1-1. Overcharge detection function

If any of the cells from V1 to V5 exceed the overcharge detection voltage, charging can be stopped by outputting "Hi impedance" from the OV output pin connecting an external pulldown resistor and turning off the charge control Nch MOS FET after the dead time set depending on values of the capacitor connecting to the COV pin. If all the cells from V1 to V5 drop below the overcharge release voltage, high level is output from the OV output pin and the overcharge detection state returns to the normal state.

Range and accuracy of detection/release voltage

• Overcharge detection voltage 3.6V to 4.5V, 5mV steps Accuracy±25mV (Topr=±0~+50°C)

Overcharge release voltage 3.4V to 4.5V, 50mV steps Accuracy±50mV

#### 1-2. Overdischarge detection function

If any of the cells from V1 to V5 drop below the overdischarge detection voltage, discharging can be stopped by outputting low level from the DCHG output pin and turning off the charge control Nch MOS FET after the dead time set depending on values of the capacitor connecting to the CDC pin.

As for the return methods from a overdischarge state to the normal state, choice is possible from two kinds of "voltage release" and "load release".

When all cells of the V1 cell - V5 cell become than the discharge reopening voltage with the IC of voltage release", output "H" level from DCHG output terminal and return to the normal state from the overdischarge detection state.

When all cells of load opening and V1 - V5 become than the discharge reopening voltage with the IC of "load release + voltage release", output "H" level from DCHG output terminal and usually return to the nomal state from the overdischarge state.

Range and accuracy of detection/release voltage

Overdischarge detection voltage 2.0V to 3.0V, 50mV steps Accuracy±80mV
 Overdischarge release voltage 2.0V to 3.4V, 50mV steps Accuracy±100mV

#### 1-3. Discharge overcurrent / short detection function

In a dischargeable state, it becomes a overcurrent detection state if the CS pin voltage exceeds the overcurrent detection voltage and drops below the short detection voltage due to load short, etc. If the CS pin voltage exceeds the short detection voltage, it becomes a short detection state. If overcurrent and short are detected, discharging can be stopped by outputting low level from the DCHG output pin and turning off the charge control Nch MOS FET after the dead time set depending on values of the capacitor connecting to the COL1 pin. The release from the overcurrent and short detection states is done by load removal. After load removal, if the V-pin voltage drops below its threshold voltage due to pulldown resistance in the IC, high level is output from the DCHG output pin and the overcurrent and short detection state returns to the normal state.

#### Range and accuracy of detection

Overcurrent detect voltage 50mV to 300mV, 5mV steps Accuracy±15mV
 Short detection voltage 0.2V to 1.0V, 50mV steps Accuracy±100mV

#### 1. Function outline of MM3474 series

#### 1-4. 3-, 4-, 5-cell protection switching function

The 3-, 4-, or 5-cell protection can be switched by connecting the SEL1 pin and SEL2 pin to the VDD or VSS2 via a protection resistor. At the time of 4-cell protection, the operation of the overcharge detection circuit and overdischarge detection circuit for the V1 cell is stopped. Therefore, short-circuit the V1 pin and VSS1 pin before use. At the time of 3-cell protection, the operation of overcharge detection circuit and overdischarge detection circuit for V1 and V2 Cell is stopped. Therefore, short-circuit the V2 pin, V1 pin and VSS1 pin before use.

SEL1 pin	SEL2 pin	MM3474 Setting
High (VDD)	High (VDD)	5 cell prptection
High (VDD)	Low (VSS2)	4 cell prptection
Low (VSS2)	High (VDD)	3 cell prptection
Low (VSS2)	Low (VSS2)	prohibite

#### 1-5. Setting function of the dead time

The MM3474 series sets overcharge detection / release dead time, overdischarge detection / release dead time, overcurrent detection / release dead time with a value of the attaching externally capacity and can change dead time by changing the fixed number of the capacity.

#### Range of detection delay time

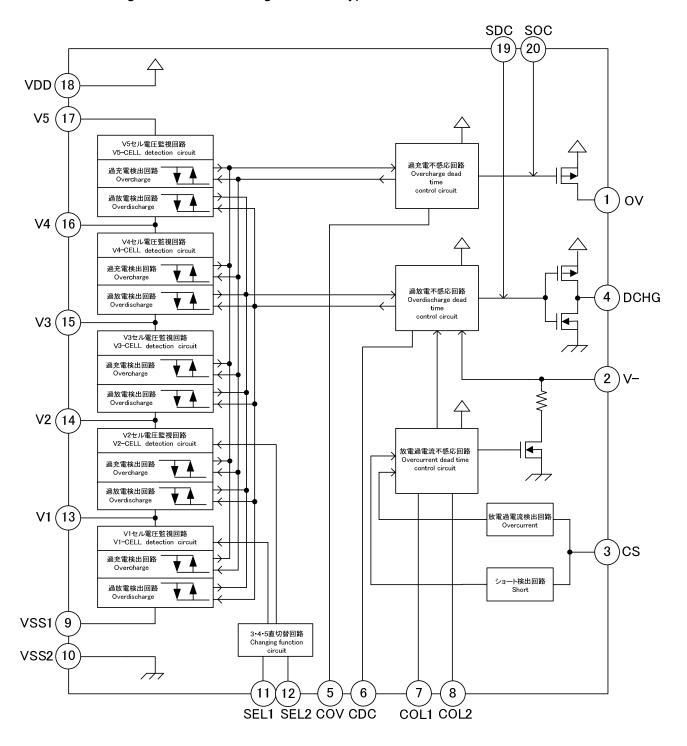
Overcharge detection/release	Setting by a capacitor of COV pin. Accuracy±50%
dead time	Detection dead time: release dead time can be set from 1:10 to 10:1.
Overdischarge detection voltage	Setting by a capacitor of CDC pin. Accuracy±50%
Overdischarge release dead time	Max.15msec fixed
<ul> <li>Overcurrent dead time</li> </ul>	Setting by a capacitor of COL1 pin. Accuracy±50%
<ul> <li>Overcurrent dead time</li> </ul>	Setting by a capacitor of COL2 pin. Accuracy±50%
<ul> <li>Short detection dead time</li> </ul>	300usec fixed

#### 1-6. Communication function when cascade connected

When using a cascade-connected IC with 6 or more cell protection, an overdischarge detection signal can be transmitted by inputting the DCHG output pin signal to the SDC pin via a resistor. If the current input to the SDC pin exceeds the SDC release current, it is recognized as normal state. If it drops below the SDC detection current or if it is open, it is recognized as overdischarge detection state. In the same way, an overdischarge detection signal can be transmitted by inputting the OV output pin signal to the SOC pin via a resistor. In addition, charge / discharge is more controllable than inputting a signal into SDC terminal, SOC terminal from the outside independently

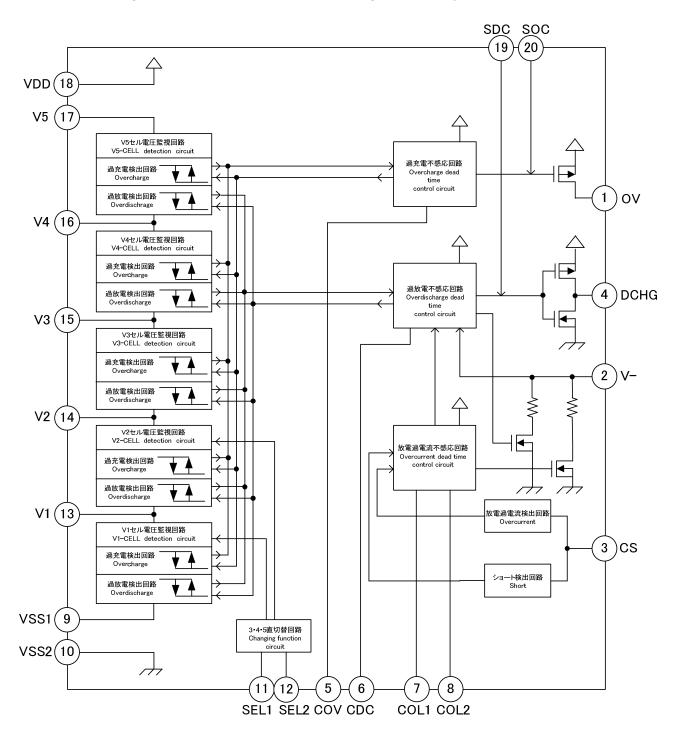
## 2. Block diagram

2-1.Overdischarge release : 「Voltage release」 type



## 2. Block diagram

2-2. Overdischarge release : 「Load release + Voltage release」 type

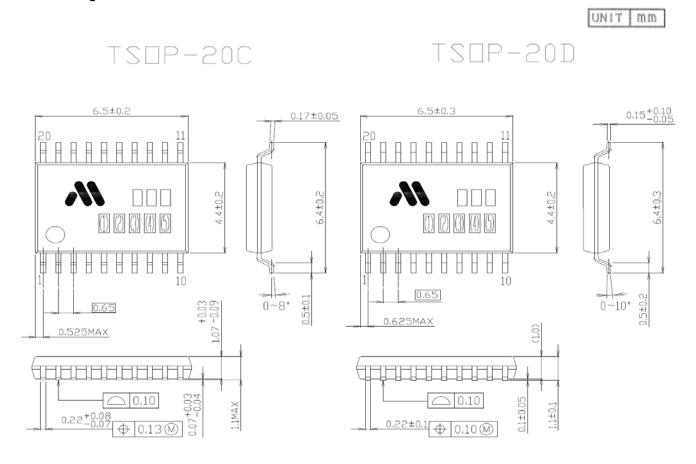


## 3. Explanation of PIN configuration and

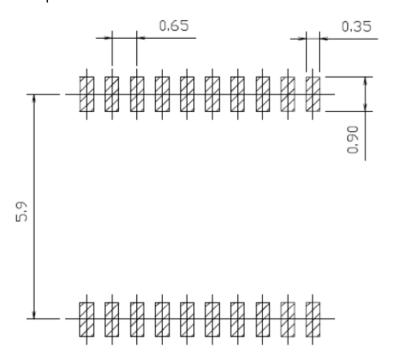
Pin No.	Pin No.	Function
1	OV	Charge control output terminal. Output type is Pch open drain. Active "Hi impedance".
2	V-	Input terminal connected to charger negative voltage. Detected charger connection and load detection.
3	CS	Input of overcurrent detection. The voltage of the sense resistance is observed, and the overcurrent is detected.
4	DCHG	Discharge control output terminal. Output type is CMOS. Active "Low".
5	COV	This pin is dead time setting of overcharge detection and release.
6	CDC	This pin is dead time setting of overdischarge detection and release.
7	COL1	This pin is dead time setting of overcurrent detection.
8	COL2	This pin is dead time setting of overcurrent release.
9	VSS1	The input terminal of the negative voltage of V1 cell .
10	VSS2	The input terminal of the ground of IC.
11	SEL1	This pin is for changing function for 3cell in series or 4cell in series , 5cell in series.  SEL1 = H , SEL2 = H → 5Cell protection
12	SEL2	SEL1 = H , SEL2 = L → 4Cell protection SEL1 = L , SEL2 = H → 3Cell protection (SEL1=SEL2=L setting is prohibited.)
13	V1	The input terminal of the positive voltage of V1 cell, and the negative voltage of V2 cell .
14	V2	The input terminal of the positive voltage of V2 cell, and the negative voltage of V3 cell .
15	V3	The input terminal of the positive voltage of V3 cell, and the negative voltage of V4 cell .
16	V4	The input terminal of the positive voltage of V4 cell, and the negative voltage of V5 cell .
17	V5	The input terminal of the positive voltage of V5 cell .
18	VDD	The input terminal of the power supply of IC.
19	SDC	The control terminal of output over discharge detection. $  _{SDC} <  _{SDC} L \rightarrow DCHG = Low $
20	SOC	The control terminal of output over charge detection. $I_{SOC} < I_{SOC} L \rightarrow OV = Hi$ impedance

## 4. Package outline and recommended land

## 4-1. Package outline



## 4-2. Recommended land pattern



## 5. Electric characteristics

Unless otherwise specified, Topr=+25°C

		(	Jniess otne	rwise spec	illea, ropr-	-+25 C
Parameter	Symbol	Conditions	Min.	Тур.	Max.	unit
	ABSOLU <sup>*</sup>	TE MAXIMUM RATINGS				
VDD pin supply voltage	$V_{VDDMAX}$		VSS2-0.3	-	+30	V
V5 pin supply voltage	$V_{V5MAX}$		V4-0.3	-	VDD+0.3	V
Voltage between the input terminals of voltage of battery	V <sub>CELLMAX</sub>		-0.3	-	+10	٧
V- pin • OV pin supply voltage	V <sub>V-MAX</sub> •V <sub>OVMAX</sub>		VDD-30	_	VDD+0.3	V
CS pin • DCHG pin supply voltage	V <sub>CSMAX</sub> •V <sub>DCHGMAX</sub>		VSS2-0.3	-	VDD+0.3	V
SEL pin supply voltage	$V_{SELMAX}$		VSS2-0.3	-	VDD+0.3	V
SDC/SOCpin supply voltage	V <sub>SDCMAX</sub>		VSS2-0.3	-	VDD+0.3	V
Storage temperature	Tstg		-55	-	+125	°C
Power dissipation	Pd		-	-	300	W
<u> </u>		D OPERATING CONDIT	IONS			I
Operating Temperature	TOPR		-40.0	-	+85	°C
Supply Voltage	VOPR		VSS2+3.5	_	VSS2+22.5	
		ENT CONSUMPTION				
Consumption current1 (Vdd)	I <sub>DD1</sub>	V <sub>CELL</sub> =4.4V	-	10.0	20.0	uA
Consumption current2 (Vdd)	I <sub>DD2</sub>	V <sub>CELL</sub> =3.5V	_	5.0	10.0	uA
Consumption current3 (Vdd)	I <sub>DD3</sub>	V <sub>CELL</sub> =1.8V	-	1.5	3.0	uA
Consumption current1 (V5)	I <sub>1V5</sub>	V <sub>CELL</sub> =4.4V	-	4.0	8.0	uA
Consumption current2 (V5)	l <sub>2V5</sub>	V <sub>CELL</sub> =3.5V	-	3.0	6.0	uA
Consumption current3 (V5)	I <sub>3V5</sub>	V <sub>CELL</sub> =1.8V	-	1.5	3.0	uA
V4·V3·V2·V1 input current	I <sub>V4</sub> •I <sub>V3</sub> •I <sub>V2</sub> •I <sub>V1</sub>	V <sub>CELL</sub> =3.5V	-	-	±300	nA
SEL input current	I <sub>SEL</sub>	V <sub>CELL</sub> =3.5V , SEL=VDD	-	0.5	1.0	uA
SDC input current	I <sub>SDC</sub>	$V_{CELL}$ =3.5V , $R_{SDC}$ =1M $\Omega$	-	0.8	1.6	uA
SOC input current	I <sub>soc</sub>	VCELL=3.5V , $R_{SDC}$ =1M $\Omega$	-	0.8	1.6	uA
D		LEASE VOLTAGE/CUR	RENT		•	
Overcharge detection voltage	$V_{CELL}U$	Ta=±0°C~+50°C	Typ-0.025	V <sub>CELL</sub> U	Typ+0.025	V
Overcharge release voltage	$V_{CELL}O$		Typ-0.050	$V_{CELL}O$	Typ+0.050	V
Overdischarge detection voltage	V <sub>CELL</sub> S		Typ-0.080		Typ+0.080	V
Overdischarge release voltage	$V_{CELL}D$		Typ-0.100	$V_{CELL}D$	Typ+0.100	V
Overcurrent detection voltage	V <sub>oc</sub>		Typ-0.015	V <sub>oc</sub>	Typ+0.015	V
V- pin overcurrent release voltage	$V_{VM}$		Typ-0.030	$V_{VM}$	Typ+0.030	V
Short detection voltage	$V_{SHORT}$		Typ-0.100	$V_{SHORT}$	Typ+0.100	
SDC detection current	I <sub>SDC</sub> L	V <sub>CELL</sub> =3.5V	-	-	0.1	uA
SDC release current	$I_{SDC}H$	V <sub>CELL</sub> =3.5V	0.5	-	-	uA
SOC detection current	I <sub>soc</sub> L	V <sub>CELL</sub> =3.5V	-	-	0.1	uA
SOC release current	I <sub>soc</sub> H	V <sub>CELL</sub> =3.5V	0.5	-	-	uA
	DETE	CTION DEAD TIME				
Overcharge detection dead time	t <sub>ov1</sub>	C <sub>COV</sub> =0.1uF	0.50	1.00	1.50	sec
Overcharge release dead time	t <sub>OV2</sub>	C <sub>COV</sub> =0.1uF	0.05	0.10	0.15	sec
Overdischarge detection dead time	t <sub>DC1</sub>	C <sub>CDC</sub> =0.1uF	0.50	1.00	1.50	sec
Overdischarge release dead time	t <sub>DC2</sub>	C <sub>CDC</sub> =0.1uF	-	-	15.0	msec
Overcurrent detection dead time	t <sub>OC1</sub>	C <sub>COL1</sub> =0.001uF	5.0	10.0	15.0	msec
Overcurrent release dead time	t <sub>OC2</sub>	C <sub>COL2</sub> =0.001uF	5.0	10.0	15.0	msec
Short detection dead time	t <sub>SHORT</sub>		100	300	600	usec

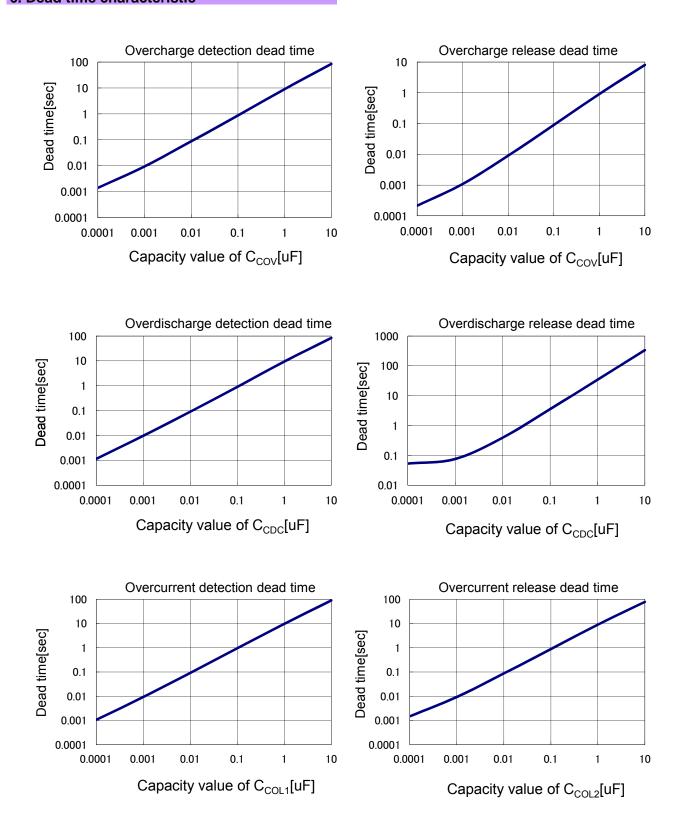
<sup>%1</sup>Dead time can be set by external capacitor.

## 5. Electric characteristics

Unless otherwise specified, Topr=+25°C

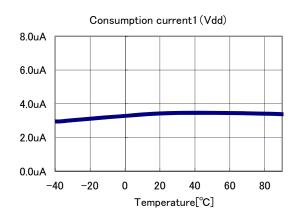
Parameter	Symbol	Conditions	Min.	Тур.	Max.	unit	
	OUTPUT PIN / SEL PIN						
DCHG source current	$I_{SO}D_{CHG}$	V <sub>DCHG</sub> =VDD-0.5V	-	-	-20	uA	
DCHG sink current	$I_{SI}D_{CHG}$	V <sub>DCHG</sub> =0.5V	20	-	-	uA	
DCHG output voltage H	$V_{TH}D_{C}H$	I <sub>SO</sub> =-20uA	VDD-0.5	-	-	V	
DCHG output voltage L	$V_{TH}D_CL$	I <sub>Si</sub> =20uA	-	-	0.5	V	
OV source current	$I_{SO}O_{V}$	V <sub>OV</sub> =VDD-0.5V	-	-	-20	uA	
Ov leak current	$I_{LEAK}O_V$	V <sub>OV</sub> =VSS2	-	-	0.1	uA	
SEL input voltage L	$V_{SEL}L$			-	0.5	V	
SEL input voltage H	V <sub>SEL</sub> H		VDD-0.5	-	-	V	
V- pin pulldown resistance	$V_{PD}$	V <sub>CELL</sub> =3.5v , V-=1V	15	30	60	kΩ	

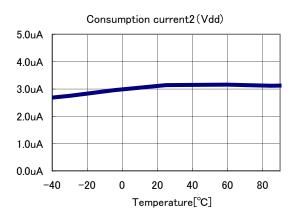
#### 6. Dead time characteristic

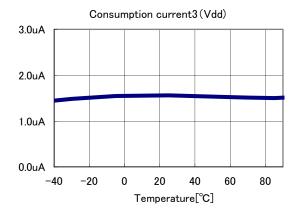


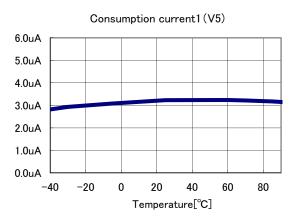
Please refer to the matters that require attention listing in P45 - P46 [11.Instruction and directions for use].

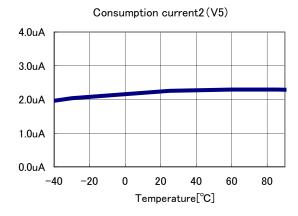
#### 7-1. Consumption current

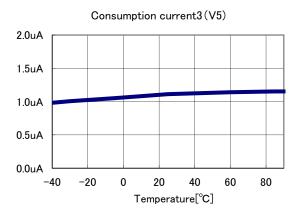




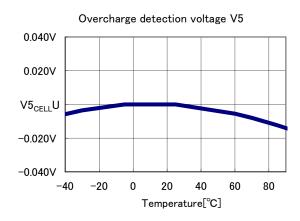


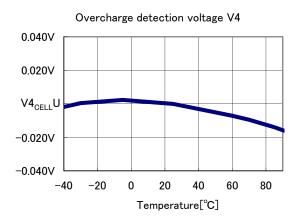


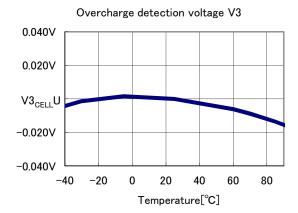


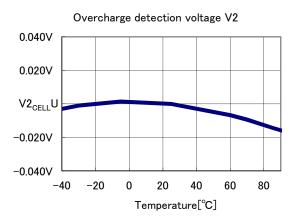


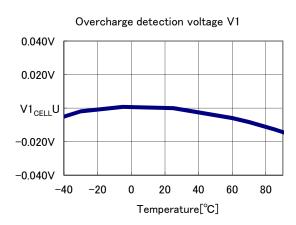
#### 7-2. Overcharge detection voltage



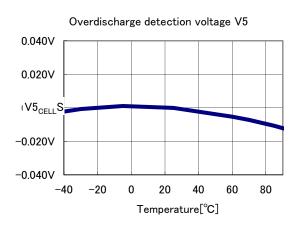


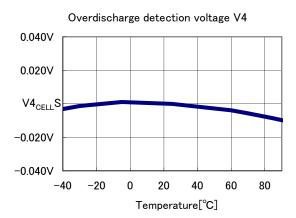


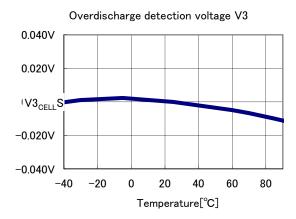


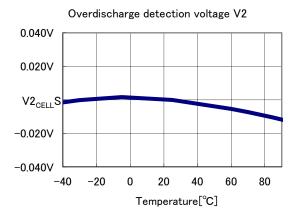


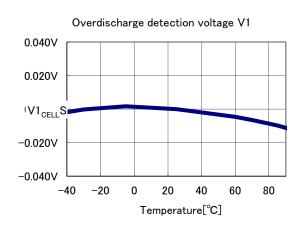
#### 7-3. Overdischarge detection voltage



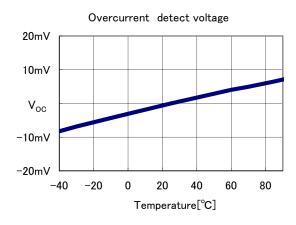


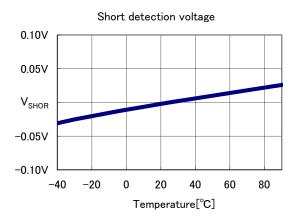


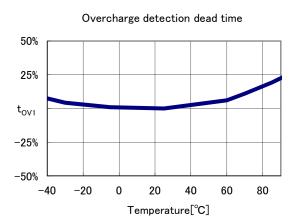


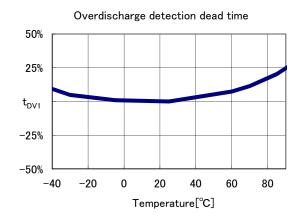


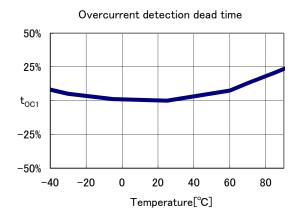
#### 7-4. Overcurrent detect voltage, Short detection voltage, Dead time

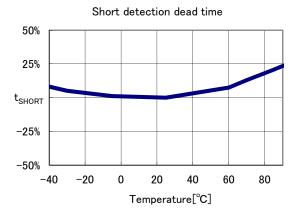




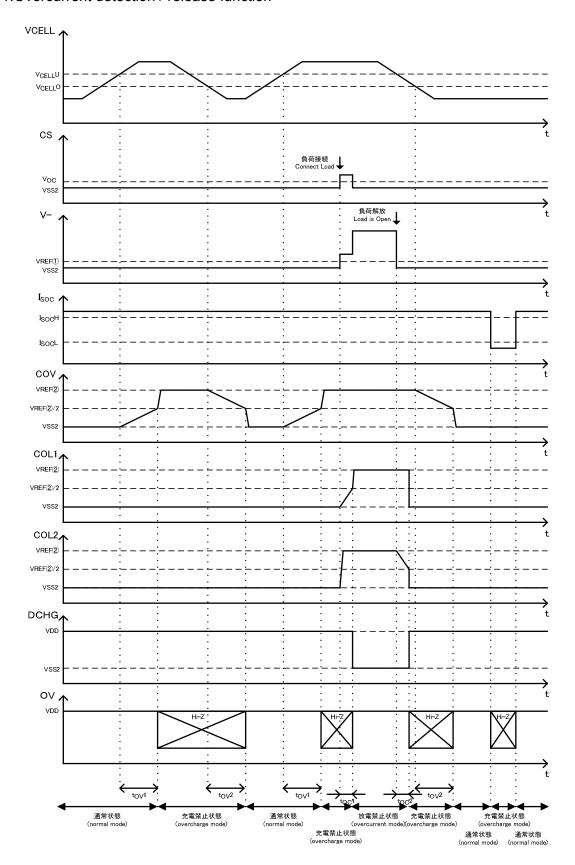




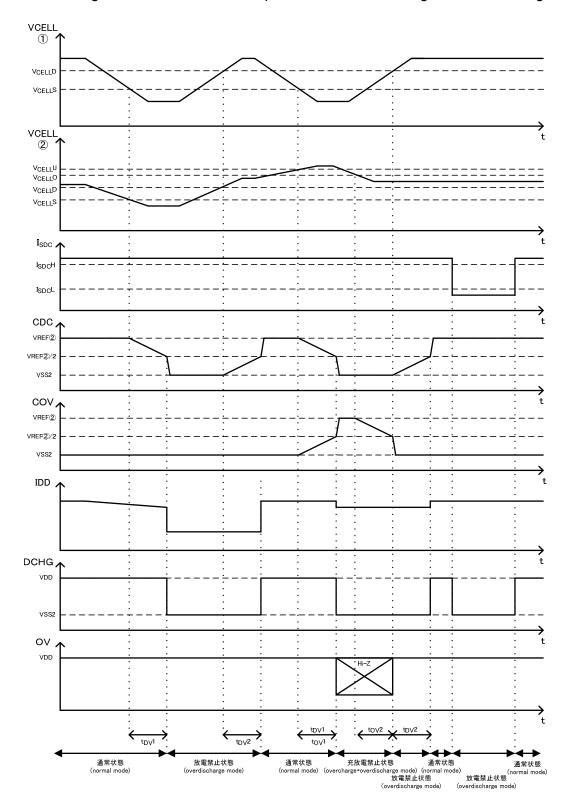




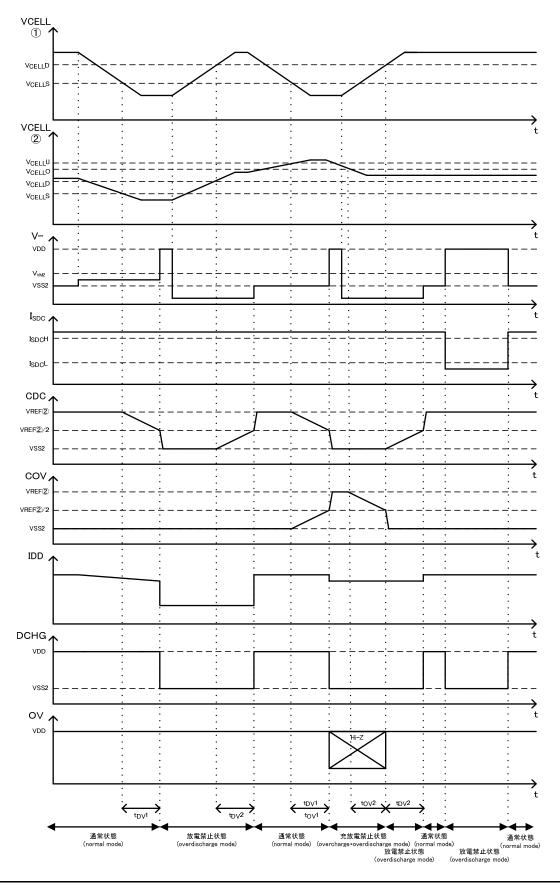
## 8-1. Overcurrent detection / release function



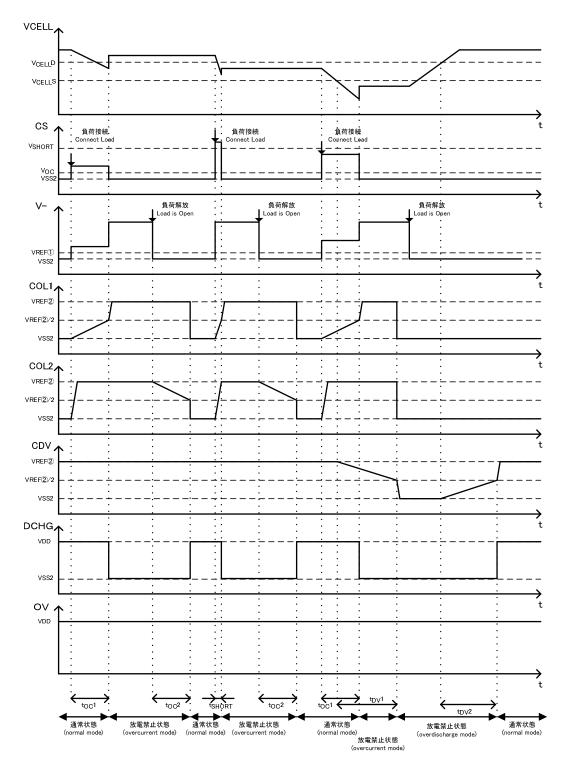
8-2. Overdischarge detection and release operation ... Overdischarge release: "Voltage release"



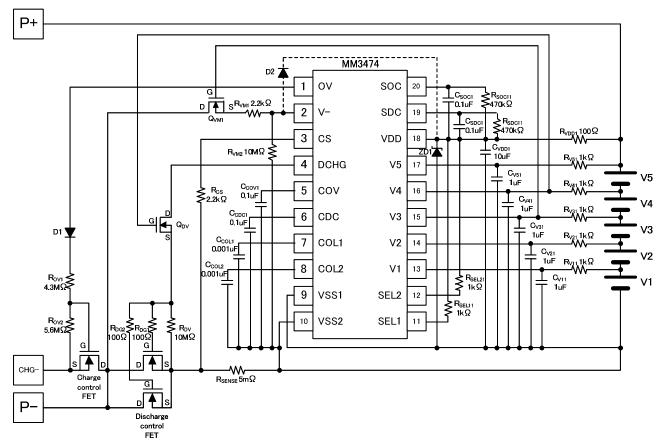
8-3. Overdischarge detection and release operation... Overdischarge release: "Load release+Voltage release" type



## 8-4. Overcurrent detection, short detection and release operation



## 9. Explanation of external parts



MM3474 5Cells protection typical application circuit

Parts name	Roles of parts			
$R_{VDD1}\!\cdot\!R_{V51}\!\cdot\!R_{V41}\!\cdot\!R_{V31}\!\cdot\!R_{V21}\!\cdot\!R_{V11}$	CR low-pass filter to stabilize a supply ripple of VDD pin·V5pin·V4pin·V3pin·V2pin·V1pin.			
$C_{VDD1} \boldsymbol{\cdot} C_{V51} \boldsymbol{\cdot} C_{V41} \boldsymbol{\cdot} C_{V31} \boldsymbol{\cdot} C_{V21} \boldsymbol{\cdot} C_{V12}$				
R <sub>SEL11</sub> •R <sub>SEL21</sub>	Resistor to protect terminal.			
R <sub>SDC11</sub> ·R <sub>SOC11</sub>	Current limitation resistor. (The voltage signal is converted into the current signal by this resistor at the cascading connection. )			
C <sub>COV1</sub>	Capacitor to sets overcharge detection/release dead time.			
C <sub>CDC1</sub>	Capacitor to sets overdischarge detection/release dead time.			
C <sub>COL1</sub>	Capacitor to sets overcurrent detection dead time.			
$C_{COL2}$	Capacitor to sets overcurrent release dead time.			
R <sub>SENSE</sub>	Sense resistance to observe discharging current.			
$R_{CS}$	Resistor to protect terminal.			
R <sub>VM1</sub>	Resistor to protect terminal.			
$R_{DG1} \cdot R_{DG2}$	Resistor for preventing the gate destruction due to parasitic oscillation.			
$\begin{array}{c} Q_{DV} \cdot R_{DV} \\ \hline R_{OV1} \cdot R_{OV2} \end{array}$	The voltage between gate and source of FET must not exceed the absolute maximum rating. Therefore, The output voltage is clamped by FET or divided with a resistor.			
Q <sub>VM1</sub> •R <sub>VM2</sub>	FET to prevent voltage input to V-pin from rising more than voltage of VDD pin.			
D1	Diode to turn off FET quickly by discharging charge of parasitic capacitance of FET.			
D2	When a V-pin becomes more than it in VDD pin voltage, it is Schottky barrier diode to bypass the electric current so that an electric current does not flow through the IC inside.			
ZD1	Zener diode to prevent destruction of IC by surge voltage.			
Charge control FET	Nch MOS FET to control charging current.			
Discharge control FET	Nch MOS FET to control discharging current.			

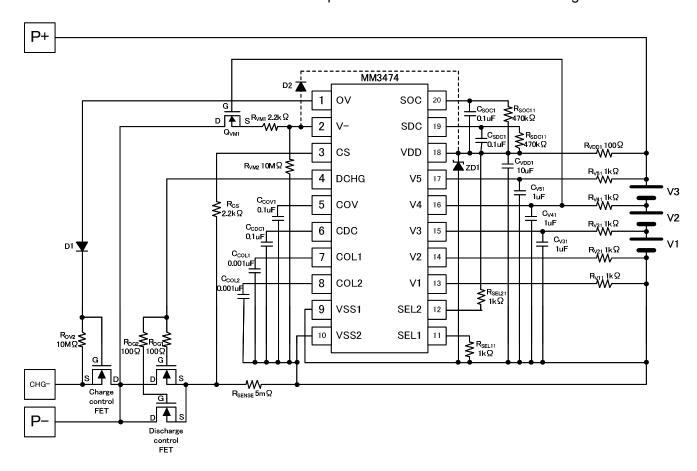
Nov 18, 2014

10-1. Examples of 3 cells application circuit

10-1-1. Circuit condition 1

Circuit condition 1

Number of cells
 Charge and discharge route
 Overdischarge release metho
 Voltage release



10-1. Examples of 3 cells application circuit

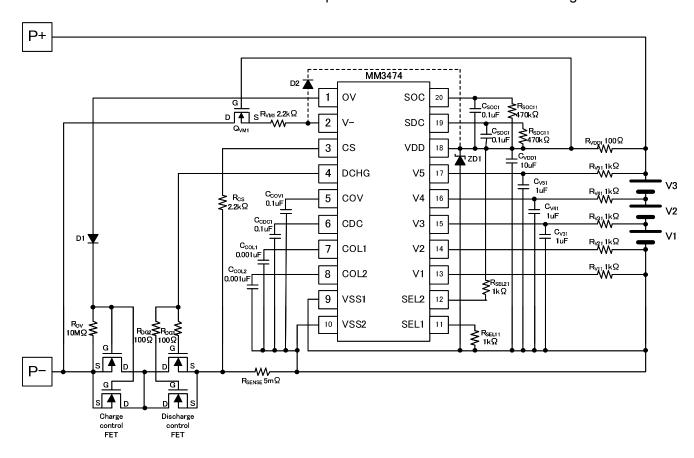
10-1-2. Circuit condition 2

Circuit condition 2

Number of cellsCharge and discharge routeCommon

• Overdischarge release metho : Voltage release

Optional functions : Nothing



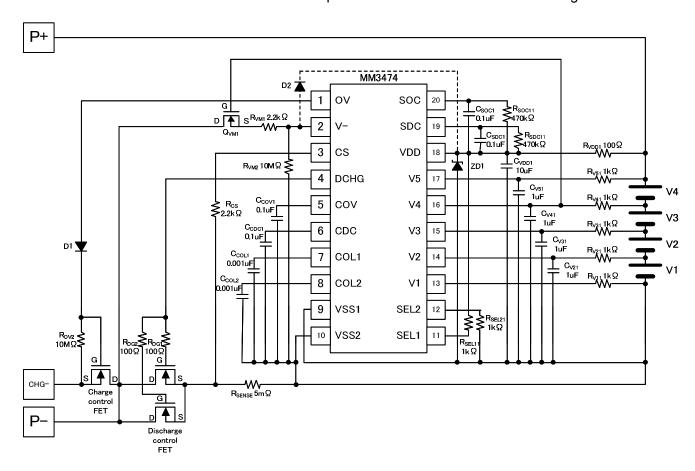
Nov 18, 2014

10-2. Examples of 4 cells application circuit

10-2-1. Circuit condition 1

Circuit condition 1

Number of cells
 Charge and discharge route
 Overdischarge release metho
 Voltage release



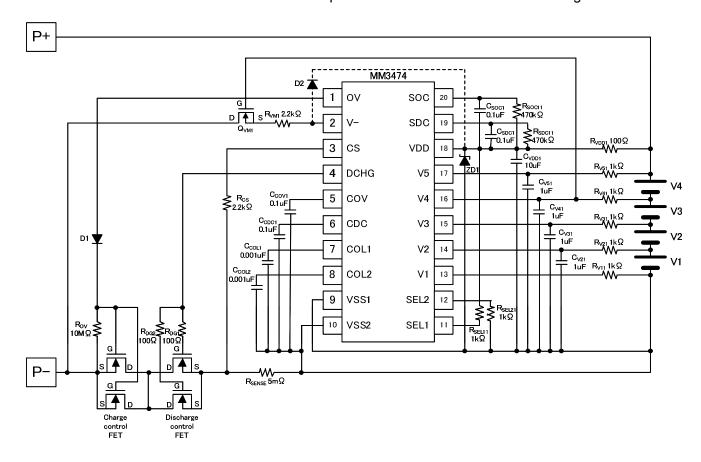
10-2. Examples of 4 cells application circuit

10-2-2. Circuit condition 2

Circuit condition 2

Number of cellsCharge and discharge routeCommon

Overdischarge release metho : Voltage release

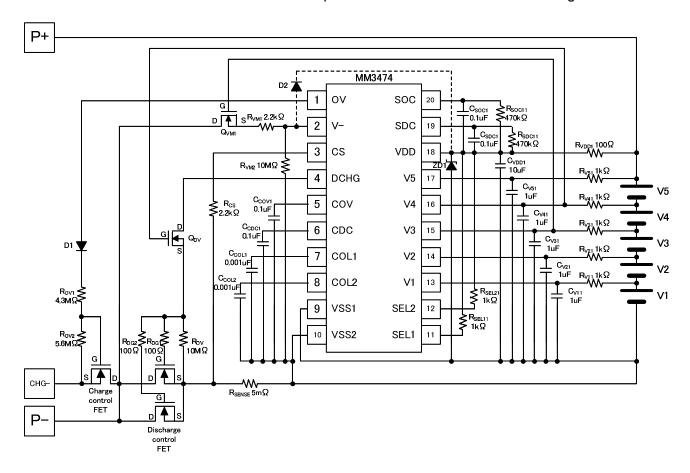


10-3. Examples of 5 cells application circuit

10-3-1. Circuit condition 1

Circuit condition 1

Number of cells
 Charge and discharge route
 Overdischarge release metho
 Voltage release



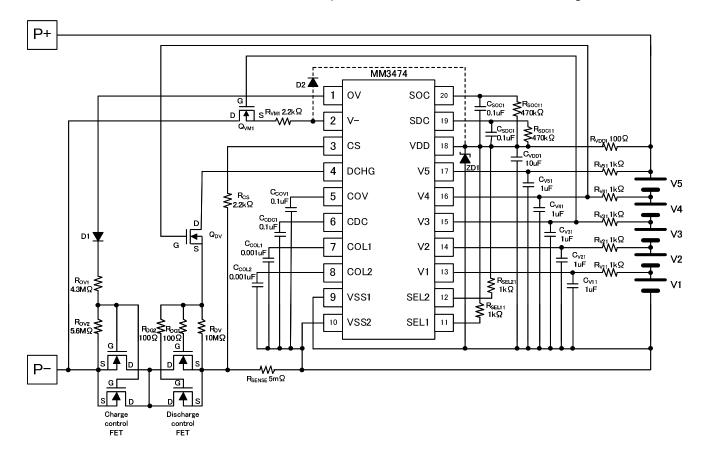
10-3. Examples of 5 cells application circuit

10-3-2. Circuit condition 2

Circuit condition 2

Number of cellsCharge and discharge routeCommon

• Overdischarge release metho : Voltage release

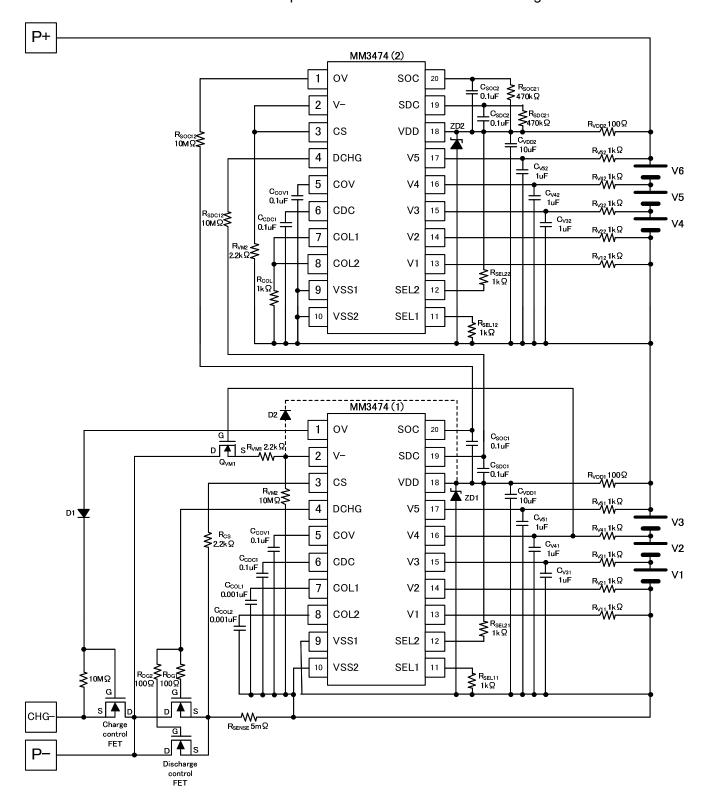


10-4. Examples of 6 cells application circl Circuit condition 1

10-4-1. Circuit condition 1 • Number of cells

Number of cells
 Charge and discharge route
 Separated

Overdischarge release metho : Voltage release



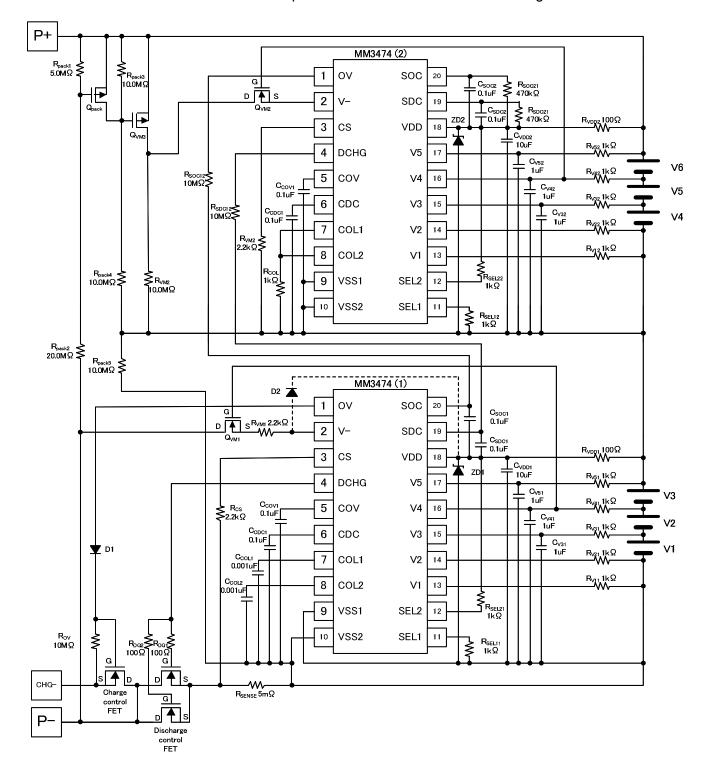
10-4. Examples of 6 cells application circl Circuit condition 2

10-4-2. Circuit condition 2 • Number of cel

Number of cells
 6 cells (3cells + 3cells)

• Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

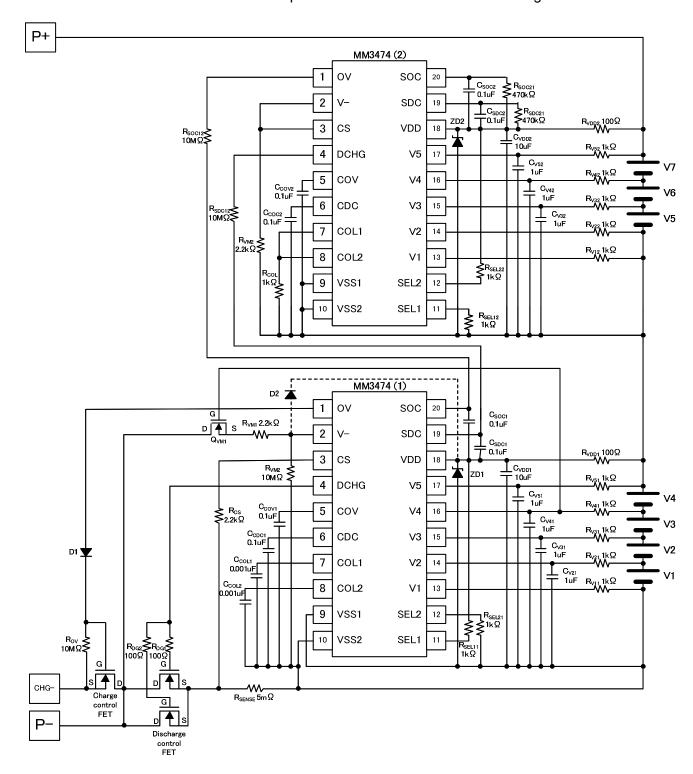


10-5. Examples of 7 cells application circl Circuit condition 1

10-5-1. Circuit condition 1 • Number of c

• Number of cells : 7 cells (4cells + 3cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release



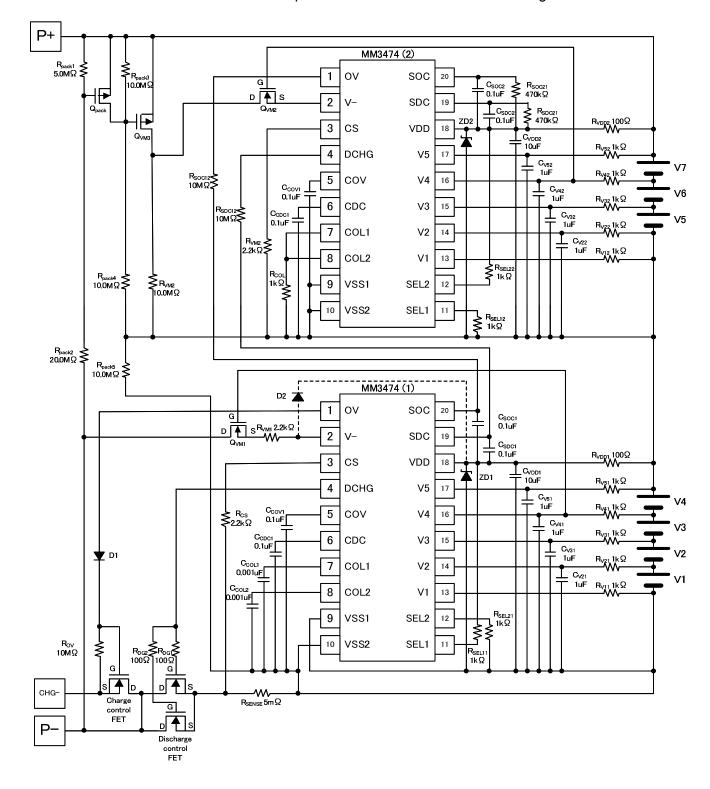
10-5. Examples of 7 cells application circl Circuit condition 2

10-5-2. Circuit condition 2 • Number of cells

• Number of cells : 7 cells (4cells + 3cells)

• Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

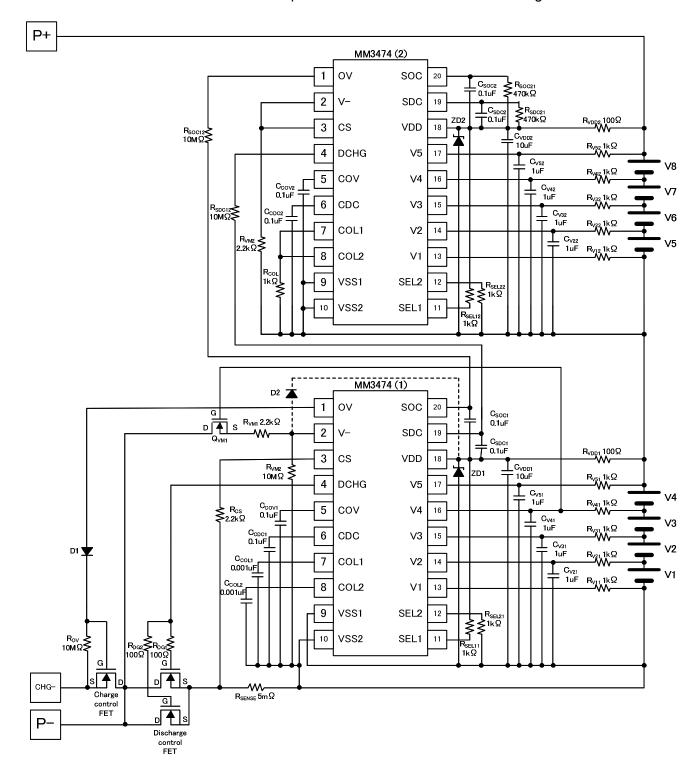


10-6. Examples of 8 cells application circl Circuit condition 1

10-6-1. Circuit condition 1 • Number of c

• Number of cells : 8 cells (4cells + 4cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release



10-6. Examples of 8 cells application circl Circuit condition 2

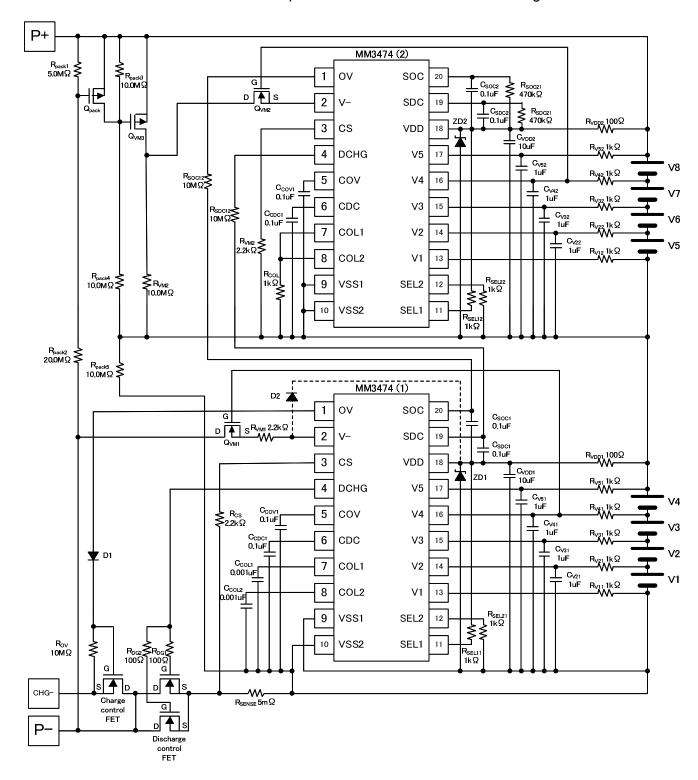
10-6-2. Circuit condition 2 N

Number of cells8 cells (4cells + 4cells)

• Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

Optional functions : Nothing



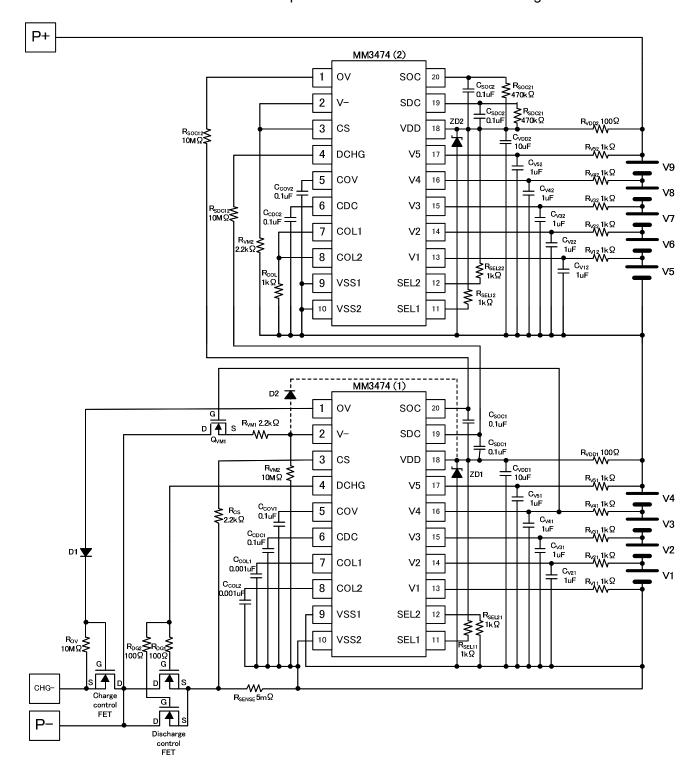
Nov 18, 2014

10-7. Examples of 9 cells application circl Circuit condition 1

10-7-1. Circuit condition 1 • Number of ce

• Number of cells : 9 cells (4cells + 5cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release



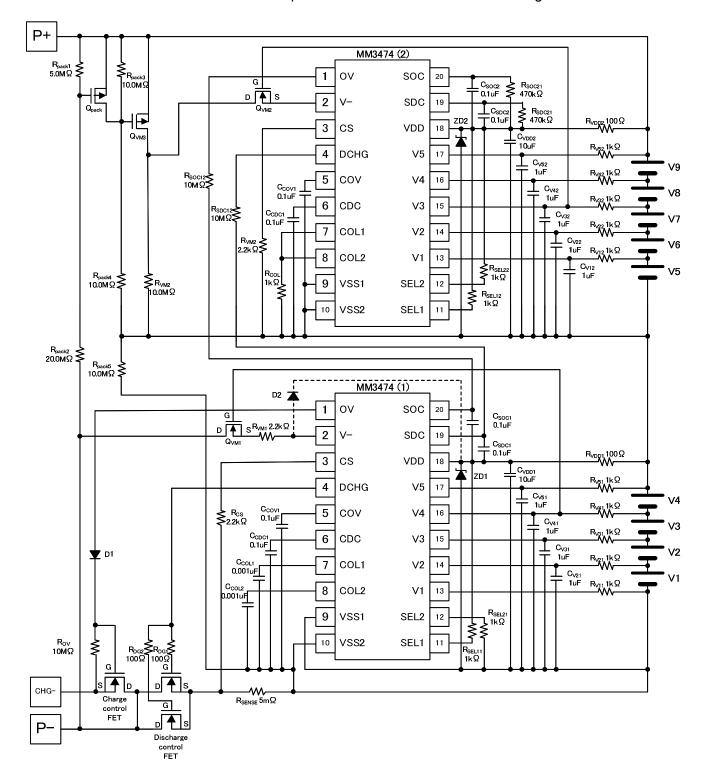
10-7. Examples of 9 cells application circl Circuit condition 2

10-7-2. Circuit condition 2 • Number of cell

• Number of cells : 9 cells (4cells + 5cells)

• Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

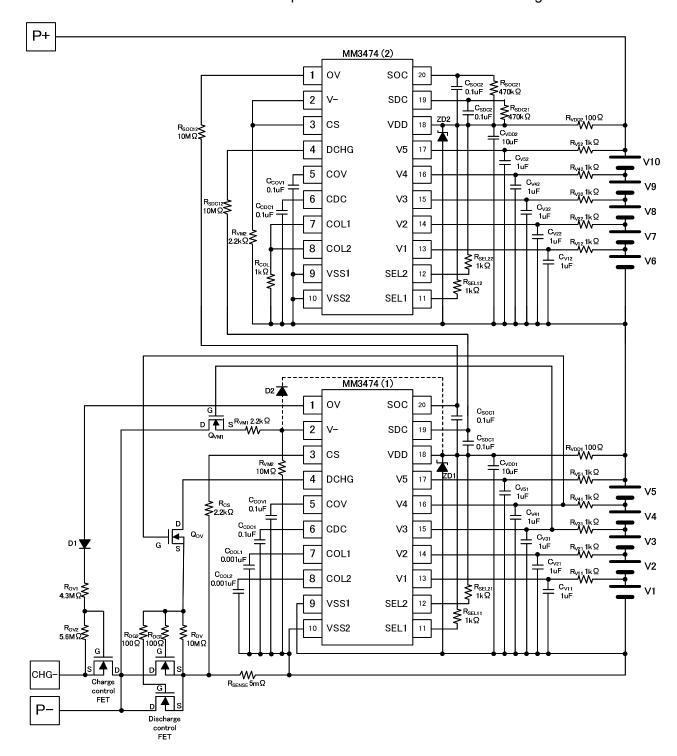


10-8. Examples of 10 cells application circ Circuit condition 1

10-8-1. Circuit condition 1 • Number of cells : 10 cells (5cells + 5cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release

Optional functions : Nothing

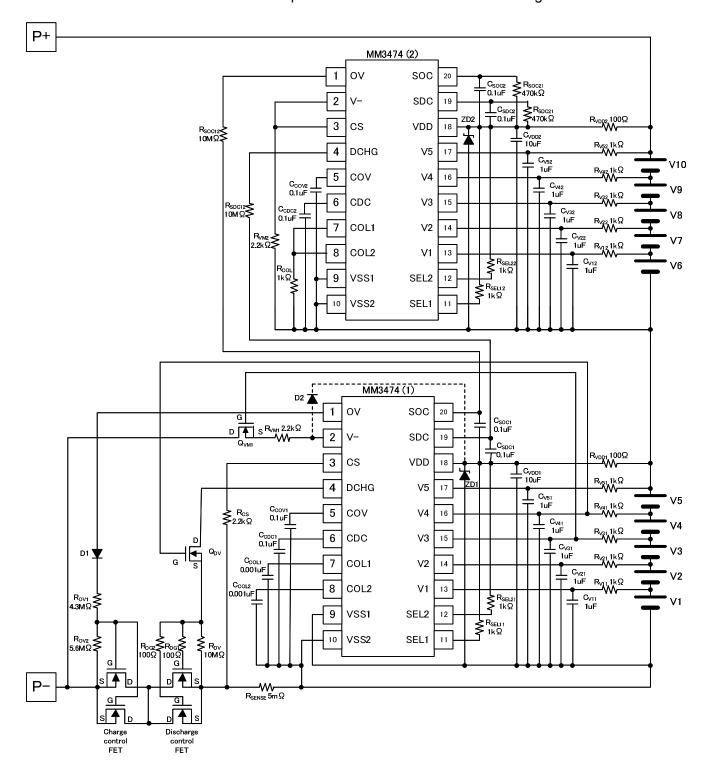


10-8. Examples of 10 cells application circ Circuit condition 2

10-8-2. Circuit condition 2 • Number of cells

Number of cellsCharge and discharge routeCommon10 cells (5cells + 5cells)Common

Overdischarge release metho : Voltage release



10-8. Examples of 10 cells application circ Circuit condition 3

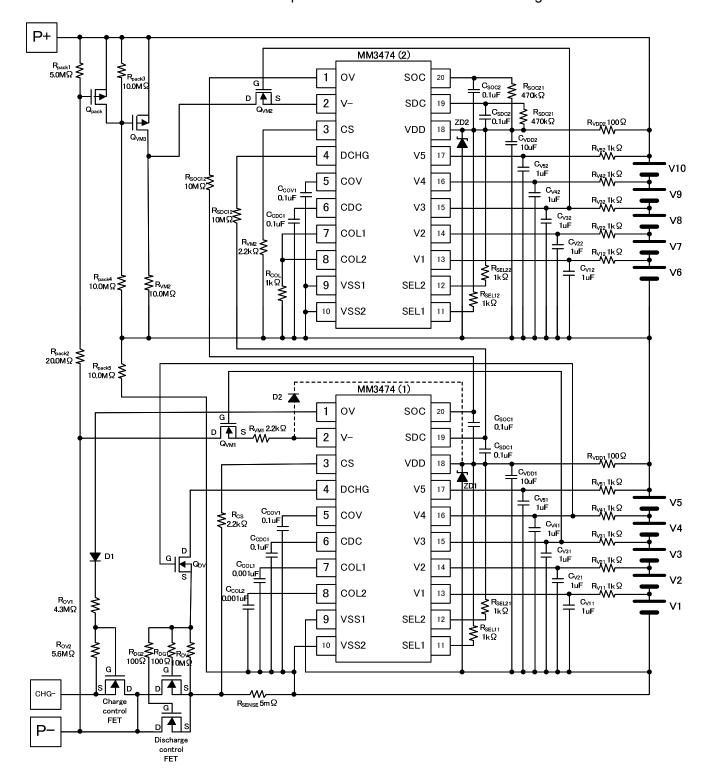
10-8-3. Circuit condition 3 • Number of cell

Number of cells
 10 cells (5cells + 5cells)

• Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

Optional functions : Nothing



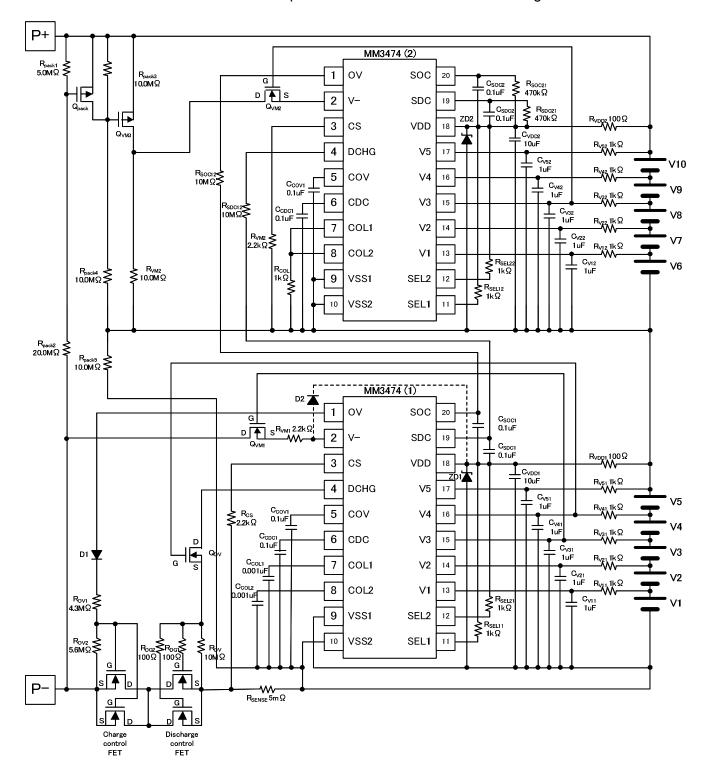
10-8. Examples of 10 cells application circ Circuit condition 4

10-8-4. Circuit condition 4 • Number of cells : 10 cells (5cells + 5cells)

Charge and discharge route : Common

Overdischarge release metho : Load release + Voltage release

Optional functions : Nothing

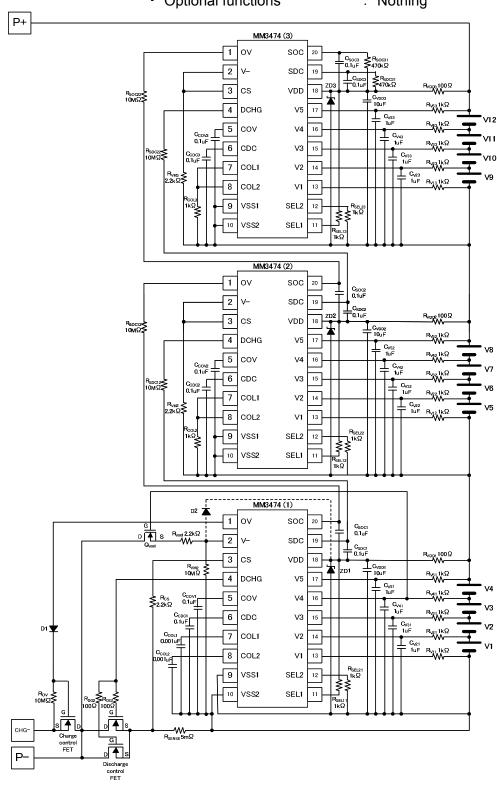


10-9. Examples of 12 cells application circuit

10-9-1. Circuit condition 1 Circuit condition 1

• Number of cells : 12 cells (4cells + 4cells + 4 cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release



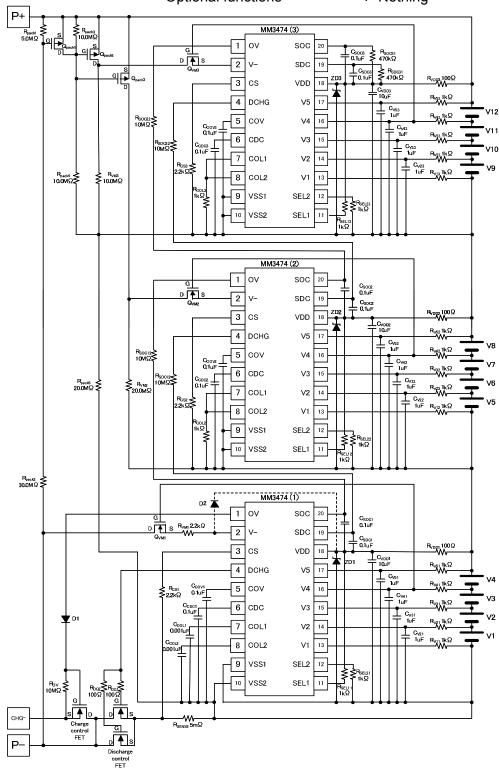
10-9. Examples of 12 cells application circuit

10-9-2. Circuit condition 2 Circuit condition 2

• Number of cells : 12 cells (4cells + 4cells + 4 cells)

Charge and discharge route : Separated

Overdischarge release metho: Load release + Voltage release

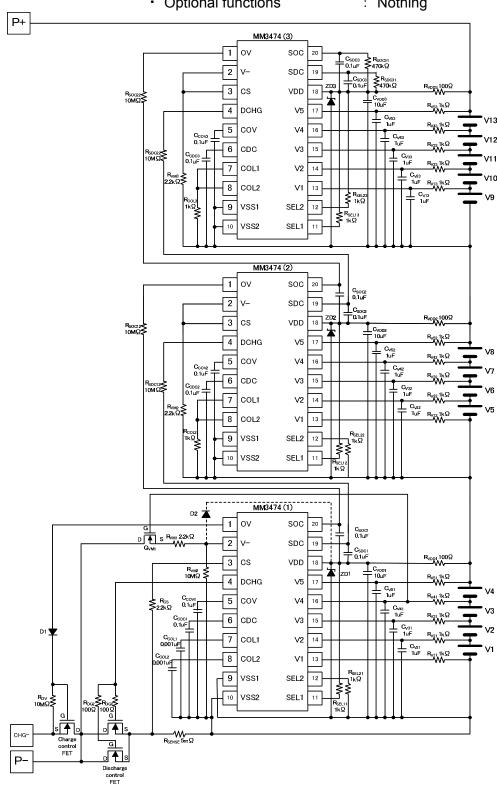


10-10. Examples of 13 cells application circuit

Circuit condition 1 10-10-1. Circuit condition 1

> : 13 cells (4cells + 4cells + 5 cells) Number of cells

 Charge and discharge route : Separated Overdischarge release metho : Voltage release



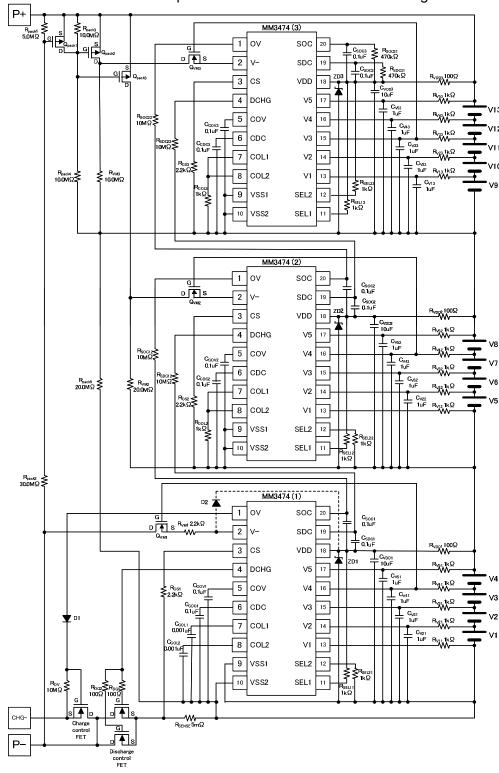
10-10. Examples of 13 cells application circuit

10-10-2. Circuit condition 2 Circuit condition 2

• Number of cells : 13 cells (4cells + 4cells + 5 cells)

Charge and discharge route : Separated

Overdischarge release metho: Load release + Voltage release

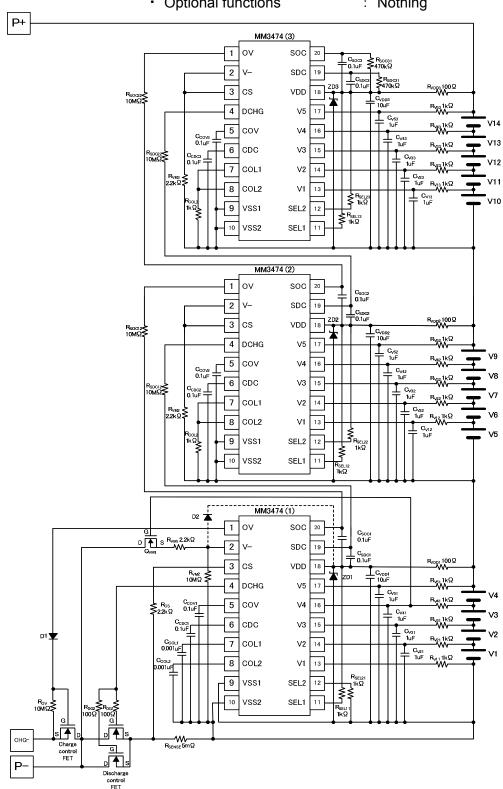


10-11. Examples of 14 cells application circuit

10-11-1. Circuit condition 1 Circuit condition 1

> : 14 cells (4cells + 5cells + 5 cells) Number of cells

Charge and discharge route : Separated Overdischarge release metho : Voltage release



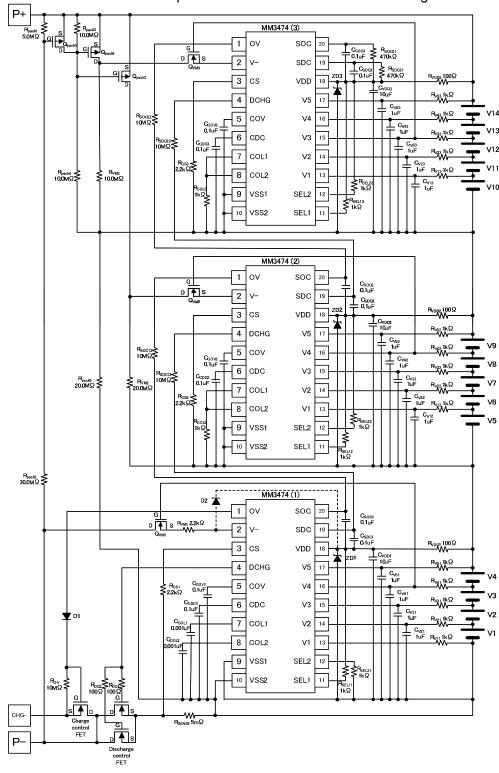
10-11. Examples of 14 cells application circuit

10-11-2. Circuit condition 2 Circuit condition 2

• Number of cells : 14 cells (4cells + 5cells + 5 cells)

Charge and discharge route : Separated

· Overdischarge release metho : Load release + Voltage release

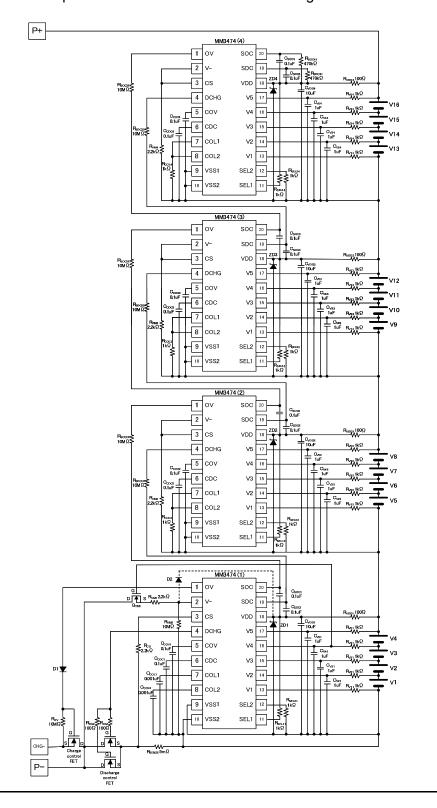


10-12. Examples of 16 cells application circuit

10-12-1. Circuit condition 1 Circuit condition 1

• Number of cells : 16 cells (4cells+4cells+4cells+4cells)

Charge and discharge route : SeparatedOverdischarge release metho : Voltage release



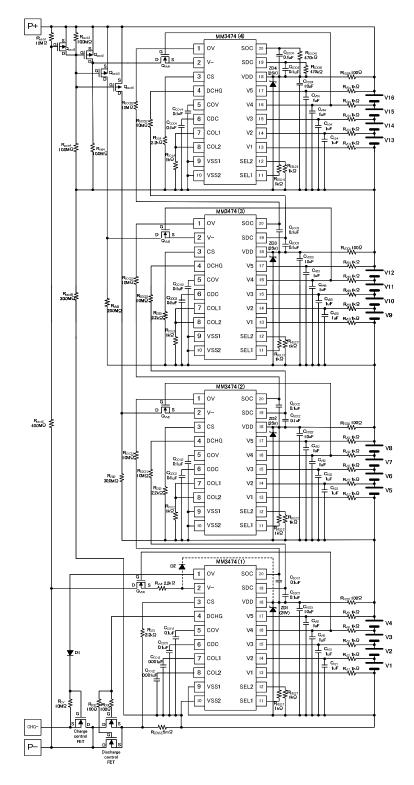
10-12. Examples of 16 cells application circuit

10-12-2. Circuit condition 2 Circuit condition 2

Number of cells
 16 cells (4cells+4cells+4cells+4cells)

Charge and discharge route : Separated

Overdischarge release metho : Load release + Voltage release

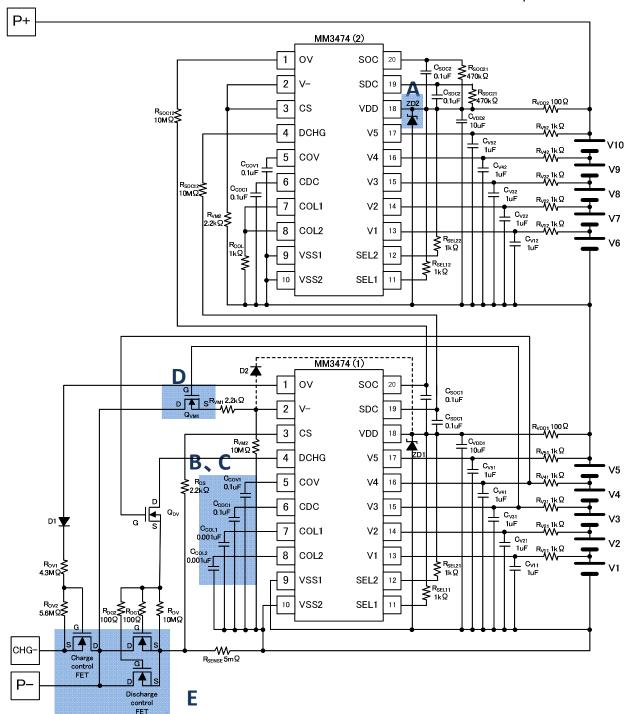


# 11. Selecting methods

Based on the following application circuits for 10-cells, recommended ranges and selecting methods for peripheral parts are shown on the Page 2 and 3. Please refer the recommended constants of parts to the following circuit example.

(1) Example of application circuit for MM3474 for 10-cells

X A - E has matters that require attention in the use.



<sup>\*</sup>This circuit is a representative application example as a reference.

Please use this IC after sufficient consideration of resistance, permissible loss and electrostatic resistance of each parts depending on the actual use environment and conditions.

# 11. Selecting methods

# (2) Recommended range and selection method for parts

<u> </u>	Circuit symbolRecommended range Selection method								
	kecommended range	Selection method							
R <sub>VDD1</sub>	$R_{VDDx}^*C_{VDDx} \rightarrow 200us \text{ or}$	These are RC low pass filters to restrain power supply of VDD pin from changing .							
C <sub>VDD1</sub>	more	To prevent malfunction, please set the time constant to 200us or more, and							
R <sub>VDD2</sub>	$R_{VDDx} \rightarrow 500\Omega$ or less	esistance value to $500\Omega$ or less. Please adjust the filter time constant of VDD pingith those of V5 to V1 pins							
$C_{VDD2}$		vith those of V5 to V1 pins.							
R <sub>V51</sub>		These are RC low pass filters to restrain power supply of V5 pin from changing. Please adjust the filter time constant of VDD pin with those of V5 to V1 pins. When supply voltage changes precipitously, V5 pin voltage beyond VDD to make parasitic element inside the IC operates, which causes malfunction. In order to							
C <sub>V51</sub>	$R_{V5x}^*C_{V5x} = R_{VDDx}^*C_{VDDx}$								
R <sub>V52</sub>									
C <sub>V52</sub>	· vox	prevent the voltage detecting of overcharge and overdischarge from being misaligned, please set the resistance value to 1kΩ or less.							
R <sub>V41</sub>	D +0 D +0	These are RC low pass filters to restrain power supply of V4 pin from changing.							
C <sub>V41</sub>	$R_{VDDx}^*C_{VDDx} = R_{V5x}^*C_{V5x}$ = $R_{V4x}^*C_{V4x}$	Please adjust the filter time constant of VDD pin with those of V5 to V1 pins. In							
$R_{V42}$	$R_{V4x} \rightarrow 1k\Omega \text{ or less}$	order to prevent voltage detecting of overcharge and overdischarge from being							
C <sub>V42</sub>	1 1/4X 11/22 OF 1000	misaligned, please set the resistance value to $1k\Omega$ or less.							
R <sub>V31</sub>	D *C -D *C	These are RC low pass filters to restrain power supply of V3 pin from changing.							
C <sub>V31</sub>	$R_{VDDx}^*C_{VDDx} = R_{V5x}^*C_{V5x}$ $= R_{V3x}^*C_{V3x}$	Please adjust the filter time constant of VDD pin with those of V5 to V1 pins. In							
R <sub>V32</sub>	$R_{V3x} \rightarrow 1k\Omega \text{ or less}$	order to prevent the voltage detecting of overcharge and overdischarge from be misaligned, please set the resistance value to $1k\Omega$ or less.							
C <sub>V32</sub>	11(V3X 11(12) 01 1000								
R <sub>V21</sub>	D *C -D *C	These are RC low pass filters to restrain power supply of V2 pin from changing. Please adjust the filter time constant of VDD pin with those of V5 to V1 pins. In							
C <sub>V21</sub>	$R_{VDDx}^*C_{VDDx} = R_{V5x}^*C_{V5x}$ = $R_{V2x}^*C_{V2x}$								
R <sub>V22</sub>	$R_{V2x} \rightarrow 1k\Omega$ or less	order to prevent the voltage detecting of overcharge and overdischarge from being misaligned, please set the resistance value to $1k\Omega$ or less.							
C <sub>V22</sub>	11000 11000								
R <sub>V11</sub>	D *C -D *C	These are RC low pass filters to restrain power supply of V1 pin from changing.							
C <sub>V11</sub>	$R_{VDDx}^*C_{VDDx} = R_{V5x}^*C_{V5x}$ $= R_{V1x}^*C_{V1x}$	Please adjust the filter time constant of VDD pin with those of V5 to V1 pins. In order to prevent voltage detecting of overcharge and overdischarge from being misaligned, please set the resistance value to $1k\Omega$ or less.							
R <sub>V12</sub>	$R_{v1x} \rightarrow 1k\Omega \text{ or less}$								
C <sub>V12</sub>	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1								
R <sub>SEL11</sub>									
R <sub>SEL21</sub>	11/01001/0	These are resistances to protect SEL1 pin and SEL2 pin.							
R <sub>SEL12</sub>	1kΩ~100kΩ	Please note that noise may cause malfunction when the resistance value is large.							
R <sub>SEL22</sub>									
R <sub>SENSE</sub>	-	This is a sense resistance for overcurrent detection. Overcurrent detection current $I_{OC}$ = Overcurrent detection voltage $V_{OC}$ / Sense resistance: $R_{SENSE}$ Please set the wattage of $R_{SENSE}$ to $I_{OC}^*V_{OC}$ or more.							
R <sub>VM1</sub>		These are pin protection resistance for V-pin.							
R <sub>VM2</sub>	1kΩ~10kΩ	In order to prevent discharge overcurrent release voltage from being misaligned, please set it to $10 k\Omega$ or less.							
Q <sub>VM1</sub>	-	This is a Nch MOS FET to prevent V-pin from increasing to VDD pin voltage or more. Even though when P- increases to VDD pin voltage or more, the maximum voltage of V-pin is limited. Please select the resistance voltage between the gate and source of FET to 20V or more; and please select the FET between drain and source with sufficient margin against the estimated voltage between P+ and P							
R <sub>cs</sub>	1kΩ~10kΩ	This is a resistance to protect CS pin. In order to prevent the detection voltage of discharge overcurrent and short from being misaligned, please set the resistance value to $10k\Omega$ or less.							

# 11. Selecting methods

(2) Recommended range and selection method for parts

	i	Selection method These are resistance and Nch MOS FET to limit the voltage between the gate a						
R <sub>DV</sub>	$R_{DV} = 1M\Omega \sim 10M\Omega$	source of discharge control FET. The voltage between the gate and source of discharge control FET is limited with the voltage that decreased by the range of						
$Q_{DV}$	-	Vgs from the gate voltage of $Q_{DV}$ . Current consumption is increased by current value of supply voltage and resistance value. Please select the resistance voltabetween the gate and source of FET to 20V or more; and please select the FET between drain and source with sufficient margin against the estimated voltage						
$R_{DG1}$	10Ω~100Ω	These are resistance to prevent FET from being destroyed by parasitic oscilla during switching DCHG pin. If FET is not used in parallel, it is not needed.						
R <sub>DG2</sub>								
R <sub>ov1</sub>	R <sub>ov1</sub> +R <sub>ov2</sub> ≒ 10MΩ	These are resistances to divide the pull down resistance and output voltage of pin. Please set the partial pressure not to over the resistance voltage between gate and source of charging control as appropriately. If it does not need to divide						
R <sub>OV2</sub>	1.00111.002	voltage, ROV1 is not necessary. Please be careful if the total resistance value i small, it may not return from discharge overcurrent and short.						
D1	-	This is a diode to prevent current from flowing into OV pin, when P- is VDD pin voltage or more. Please set a diode with sufficient margin against the voltage between P+ and P- for the resistance voltage of opposite side.						
R <sub>SDC21</sub>	500kΩ or less	These are resistances to limit pin current of SDC pin. To prevent miss detect must be $500k\Omega$ or less. When resistance value decreases, noise resistance						
R <sub>SOC21</sub>	0001122 01 1033	increases and pin current also increases.						
R <sub>SDC12</sub>	- 8M∼14M	These are resistances to transmit the voltage signal of OV pin and DCHG pin to the lower SOC pin and SDC pin. Please set it to $14M\Omega$ or less to prevent miss detection. Please pay attention, when it is $8M\Omega$ or less. SDC and SOC pin may						
R <sub>SOC12</sub>		detection. Please pay attention, when it is $8M\Omega$ or less, SDC and SOC pin may over VDD pin to cause malfunction.						
C <sub>SDC1</sub>								
C <sub>SDC2</sub>	0.1uF	These are capacitors to prevent miss detection when VDD pin voltage changes						
C <sub>SOC1</sub>	_	suddenly.						
C <sub>SOC2</sub>								
C <sub>COV1</sub>	4							
C <sub>CDC1</sub>	4							
C <sub>COL1</sub>	100pF or more	These are capacitors to set insensitive time. Please set the constant number of						
C <sub>COL2</sub>	C <sub>COL1</sub> :C <sub>COL2</sub> =1:100~	capacitor depending on the insensitive time which you want to set.  When the capacity value is 100pF or less, circuit delay affects insensitive time.						
C <sub>CDC2</sub>	$C_{CDC} > C_{COL1}$	Please confirm the actual application before using.						
C <sub>COV3</sub>	-							
C <sub>CDC3</sub>								
ZD1	24~30V	This is a zener diode to prevent IC from being destroyed by surge voltage.						
D2	-	This is a diode to prevent the current from flowing into the parasite element insi of IC even when V pin increases up to VDD pin or more.  When it is beyond cramping lower than the VDD pin voltage because of the parasitic inductance elements of board etc., please insert it depending on the necessity. Schottky diode is recommended.						

<sup>\*</sup>The above constants provide no guarantees for actual operation. Sufficient evaluation with actual application is needed before selecting the constant.

#### 12. Instructions and directions for use

- A. In order to prevent IC destruction by serge voltage, it is recommended to insert zener diode where is close to the pin between VDD and VSS of IC.
- B. If overdischarge release method is voltage release type, please set CCDC>CCOL1, in order that overcurrent detection delay time becomes shorter than overdischarge detection delay time. When cell voltage becomes less than overdischarge detection voltage during over current discharge and overdischarge is detected before overcurrent, overdischarge detection and release may be repeated.
- C. If the method of overcharge release is voltage release type and the range of voltage changed by charge current and cell impedance is larger than overcharge hysteresis voltage, overcharge detection and release are repeated. With consideration of heat value of charge control FET, please set the C<sub>COV</sub> value.
- D. Q<sub>VM1</sub> is a part to clamp in order to prevent the voltage which is input to V-pin from exceeding the maximum rating. In any case which P- increases more than VDD, the maximum voltage of V-pin is kept as below value. V-pin voltage < Gate voltage of Q<sub>VM1</sub> Gate cut off voltage of Q<sub>VM1</sub>With consideration of minimum voltage of cells under each detection condition, please choose Q<sub>VM1</sub> which meets the following conditions without fail.
  - (1) VDD ( Gate voltage of Q<sub>VM1</sub> Gate cut off voltage of Q<sub>VM1</sub> ) > 1.5V \*when overdischarge is detected output circuit is 1.5V. When the voltage between VDD pin and V-pin becomes 1.5V or less, output of OV pin may be high impedance.
    For the circuit of which charge and discharge route is separated, the voltage of V-pin may not be lowered even battery charger is connected and battery may not be able to be charged.
  - (2) Gate voltage of Q<sub>VM1</sub> Gate cut off voltage of Q<sub>VM1</sub> > V<sub>VM</sub> \*When overcurrent or short detected If V-pin voltage doesn't increase beyond V<sub>VM</sub> during overcurrent or short detection, detection condition may not be maintained and detection and release may be repeated . Voltage of the total voltage of all cells or more may be impressed between the source of Q<sub>VM1</sub> and drain. Please select parts with sufficient margin of Q<sub>VM1</sub> resistance voltage.
- E. It is recommended to branch the wiring from the drain of charge and discharge control FET when charge and discharge route is divided.

# 13. Products line up list

			Detect	ion / Re	elease v	oltage			Detect	ion / Re	elease v	oltage		Optional function
Status of current IC	Product name (MM3474)	Overcharge detection voltage	Overcharge release voltage	$\left. egin{array}{c} < \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	Overdischarge release voltage	Overcurrent detection voltage	Short detection voltage	Overcharge detection dead time	Sovercharge release dead time	Overdischarge detection dead time	Overdischarge release dead time	Overcurrent detection dead time	Overcurrent release dead time	Overdischarge release
		V	V	V	V	mV	V	sec	msec	sec	msec	msec	msec	<b>※</b> 1
MP	C01VBE	4.250	4.150		3.000	250	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	C02VBE	4.250	4.150		2.600	250	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	C03VBE	4.250	4.150		3.000	250	0.80	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	C04VBE	4.250	4.150	2.800	3.000	150	0.25	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
ES	C05VBE	4.250	4.150	2.800	3.000	150	0.25	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	D01VBE	3.850	3.650	2.300	2.500	150	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	D03VBE	3.800	3.600	2.000	2.500	150	0.60	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	E01VBE	4.250	4.150	2.800	3.000	150	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	E02VBE	4.200	4.100	2.800	3.000	150	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	E03VBE	4.175	4.100	2.800	3.000	150	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	E04VBE	4.250	4.150	2.800	3.000	100	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	E05VBE	4.250	4.150	2.800	3.000	50	0.40	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	F01VBE	4.250	4.150	2.500	3.000	150	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	F02VBE	4.200	4.100	2.500	3.000	100	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	F03VBE	4.250	4.150	2.500	3.000	100	0.30	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
MP	F04VBE	4.250	4.210	2.500	3.000	100	0.80	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	F05VBE	4.250			3.000	100	0.25	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	F06VBE	4.225	4.150	2.000	3.000	50	0.20	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	F08VBE	4.400	4.300	2.500	3.000	120	0.25	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	F11VBE	4.400	4.300	2.500	3.000	150	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	F12VBE	4.250	4.150	2.500	3.000	200	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	G01VBE	4.200	4.100	2.750	3.000	100	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	G02VBE		4.150		3.000	100	1.00	1.0	0.1	1.0	Max.15		10.0	Non Latch
MP	G03VBE		4.100		3.000	100	0.40	1.0	0.1	1.0	Max.15		10.0	Non Latch
MP	G05VBE		4.150		3.000	100	0.40	1.0	0.1	1.0	Max.15		10.0	Non Latch
MP	G06VBE		4.100		3.000	100	0.80	1.0	0.1	1.0	Max.15		10.0	Non Latch
MP	G07VBE		4.150		3.000	100	0.20	1.0	0.1	1.0	Max.15		10.0	Non Latch
ES	J01VBE		4.100		3.000	50	1.00	1.0	0.1	1.0	Max.15		10.0	Non Latch
ES	K02VBE	4.250	4.100	3.000	3.225	100	0.40	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch

%1 Non Latch : voltage release Latch : voltage release + load remove

Please inquire to us, if you request a rank other than the above.

# 13. Products line up list

		Detection / Release voltage						Detection / Release voltage						Optional function
Status of current IC	Product name (MM3474)	Overcharge detection voltage	Overcharge release voltage	Overdischarge detection voltage	Overdischarge release voltage	Overcurrent detection voltage	Short detection voltage	Overcharge detection dead time	Overcharge release dead time	Overdischarge detection dead time	Overdischarge release dead time	Overcurrent detection dead time	Overcurrent release dead time	Overdischarge release
			V <sub>CELL</sub> O		V <sub>CELL</sub> D	V <sub>oc</sub>	$V_{SHORT}$	t <sub>OV1</sub>	t <sub>OV2</sub>	t <sub>DC1</sub>	t <sub>DC2</sub>	t <sub>OC1</sub>	t <sub>OC2</sub>	<b>%</b> 1
F0	1(00) (DE	V	V	V	V	mV	V	sec	msec	sec	msec	msec	msec	1 - 1 - 1
ES	K03VBE K04VBE	4.250	4.190	3.000	3.200 3.200	80	0.70	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
MP MP	L02VBE	4.175 3.750	4.100 3.550	2.200	2.700	100	0.50 0.40	1.0	0.1	1.0	Max.15 Max.15	10.0	10.0	Non Latch Non Latch
MP	L02VBE	3.650	3.500	2.000	2.700	200	0.40	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	L04VBE	3.750	3.550		2.700	100	0.40	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
MP	M01VBE	4.350	4.150	2.300	3.000	150	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	N01VBE	3.900	3.600	2.000	3.000	100	0.20	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
MP	P03VBE	4.230	4.220	2.800	3.400	100	0.80	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
ES	P04VBE	4.200	4.170	2.750	2.800	100	1.00	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	P05VBE	4.200	4.140	2.750	2.810	100	0.50	1.0	0.1	1.0	Max.15	10.0	10.0	Latch
ES	P06VBE	4.230	4.220	2.800	3.000	100	0.80	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch
MP	S01VBE	3.600	3.500	2.800	3.000	100	0.40	1.0	0.1	1.0	Max.15	10.0	10.0	Non Latch

%1 Non Latch : voltage release Latch : voltage release + load remove

Please inquire to us, if you request a rank other than the above.

# 14. Introduction of releted products

14-1. MM3220V series : 2-Cells Li-ion Battery protection IC

#### Outline

MM3220V series are used by an application of 6- cells and 7- cells etc in cascade connection with MM3474 series. It's possible to make it the composition in low cost and space-saving by using MM3220 V series. It's connected with MM3474 easily by making the output form a Pch open drain.

#### Main characteristics

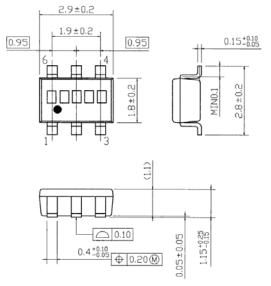
Overcharge detection voltage	3.6V~4.5V, 5mV steps	Accuracy±25mV (Topr=-5~+60°C)
Overcharge release voltage	3.4V~4.5V, 50mV steps	Accuracy±50mV
Overdischarge detection voltage	2.0V~3.0V, 50mV steps	Accuracy±80mV
Overdischarge release voltage	2.0V~3.4V, 50mV steps	Accuracy±100mV

# Package outline and PIN configuration

MM3220V series PIN configuration ... SOT-26A

Top view	Pin No.	Symbol	Function
0 5 4	1	DOUT	Output of overdischarge detection. Output type is Pch open drain.
6 5 4	2	COUT	Output of overcharge detection. Output type is Pch open drain.
	3	V-	Input terminal connected to charger negative voltage.
	4	VBL	Input terminal of the low side cell.
1 2 3	5	VDD	Input terminal of the high side cell. Supply terminal.
	6	VSS	VSS terminal. Connected to ground

unit: mm



SOT-26A

# 14. Introduction of releted products

14-2. MM3513 series : Voltage monitor IC for Li-ion cell balance

#### Outline

It's possible to add a cell balance control function by connecting MM3513 to each cell. When MM3513 senses that the cell voltage exceeds detecting voltage, Cell balance control is performed by bypassing charging current of the cell by NchMOSFET and external resistance.

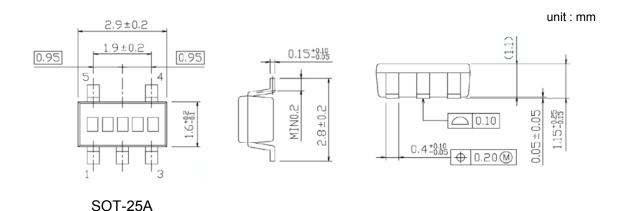
Main characteristics

detection voltage 3.5V~4.5V, 5mV steps Accuracy±20mV,

Accuracy±25mV (Topr=-5~+60°C)

# Package outline and PIN configuration

Top view SOT-25A	Pin No.	Symbol	Function
5 4	1	NC	No connection.
	2	VDD	Connected to IC substrait.
	3	VSS	Connected to ground.
	4	DS	Delay shorten terminal.
1 2 3	5	OUT	Output of detecting voltage. Output type is CMOS.



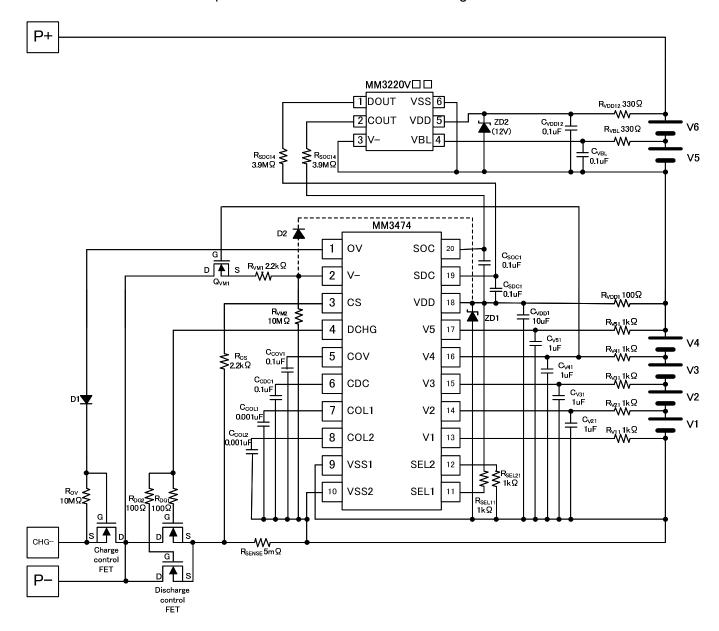
15-1. Examples of circuit using 2cell protection MM3220V

15-1-1. Circuit condition 1 Circuit condition 1

Number of cells
 6cells (4cells+2cells)

Charge and discharge route : SeparatedOverdischarge release methc : Voltage release

Optional functions : Nothing



15-1. Examples of circuit using 2cell protection MM3220V

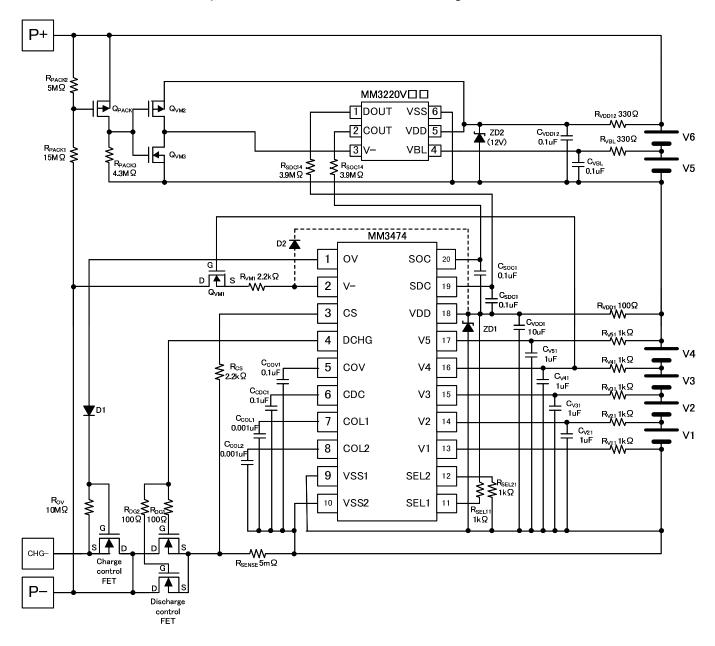
15-1-2. Circuit condition 2 Circuit condition 2

Number of cells6cells (4cells+2cells)

Charge and discharge route : Separated

Overdischarge release methc : Load release + Voltage release

Optional functions : Nothing

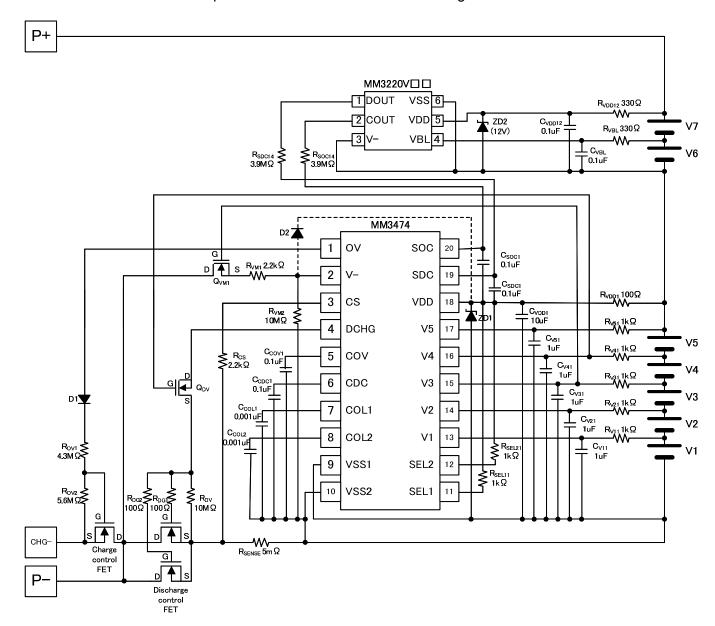


15-1. Examples of circuit using 2cell protection MM3220V

15-1-3. Circuit condition 3 Circuit condition 3

Number of cells
 7cells (5cells+2cells)

Charge and discharge route : SeparatedOverdischarge release methc : Voltage release



15-1. Examples of circuit using 2cell protection MM3220V

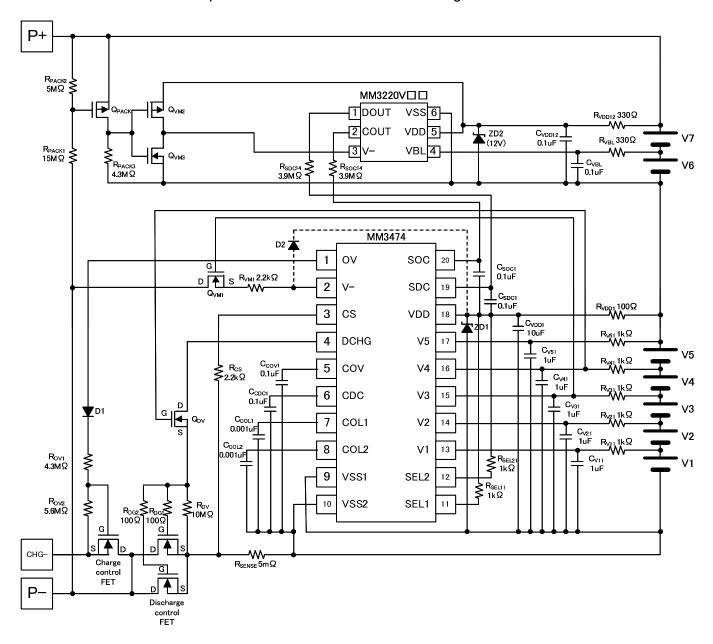
15-1-4. Circuit condition 4 Circuit condition 4

Number of cells7cells (5cells+2cells)

Charge and discharge route : Separated

Overdischarge release methc : Load release + Voltage release

Optional functions : Nothing

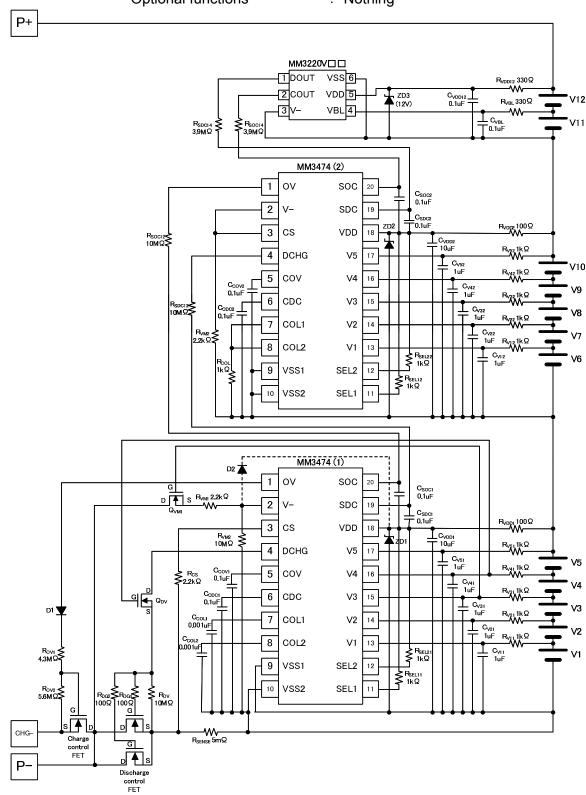


15-1. Examples of circuit using 2cell protection MM3220V

15-1-5. Circuit condition 5 Circuit condition 5

Number of cells
 12cells (5cells+5cells+2cells)

Charge and discharge route : SeparatedOverdischarge release methc : Voltage release



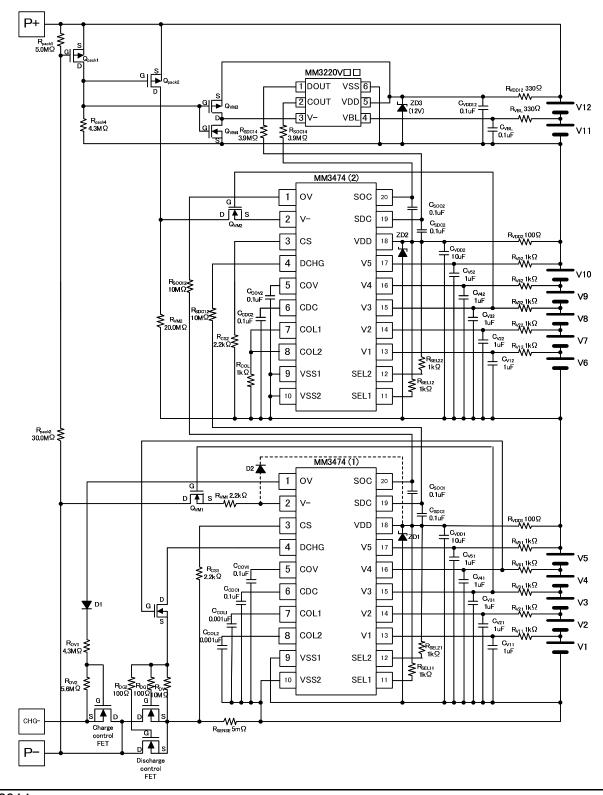
15-1. Examples of circuit using 2cell protection MM3220V

15-1-6. Circuit condition 6 Circuit condition 6

Number of cells
 12cells (5cells+5cells+2cells)

Charge and discharge route : Separated

Overdischarge release methc : Load release + Voltage release

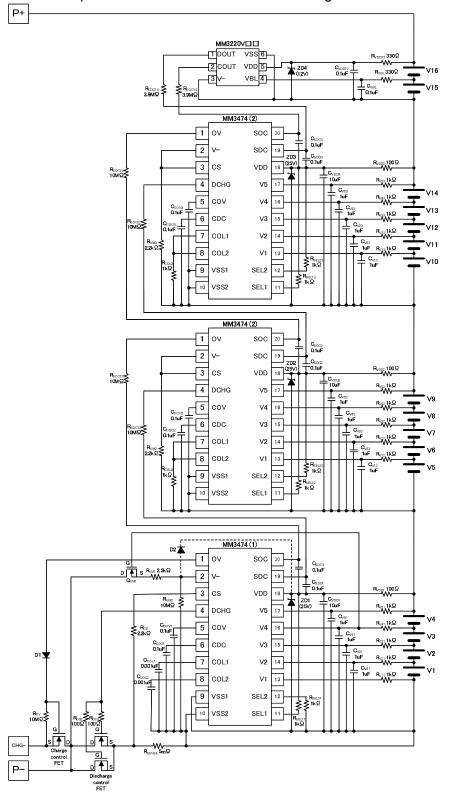


15-1. Examples of circuit using 2cell protection MM3220V

15-1-7. Circuit condition 7 Circuit condition 7

Number of cells
 16cells (4cells+5cells+5cells+2cells)

Charge and discharge route : SeparatedOverdischarge release methc : Voltage release



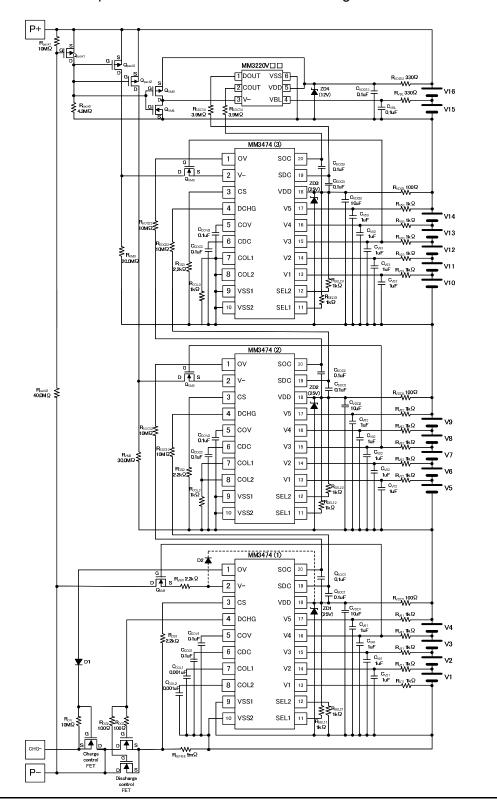
15-1. 2 Examples of circuit using 2cell protection MM3220V

15-1-8. Circuit condition 8 Circuit condition 8

Number of cells
 16cells (4cells+5cells+5cells+2cells)

Charge and discharge route : Separated

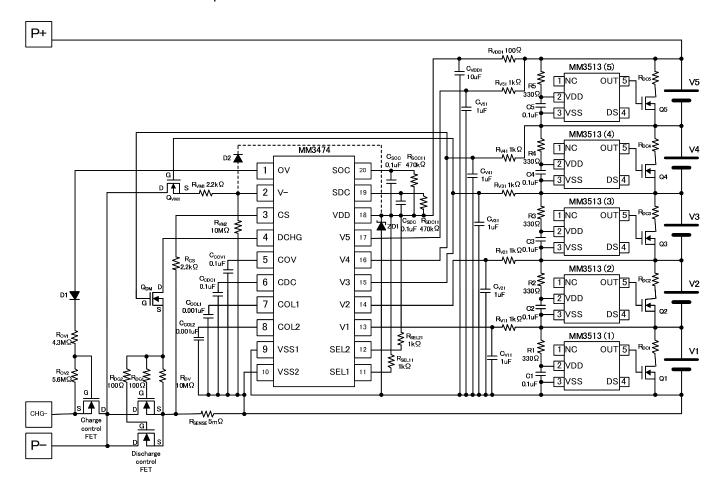
Overdischarge release methc : Load voltage + Voltage release



15-2. Examples of circuit using cell balance MM3513

15-2-1. Circuit condition 1 Circuit condition 1

Number of cells
 Charge and discharge route
 Overdischarge release methc
 Optional functions
 Scells
 Separated
 Voltage release
 Cell balance

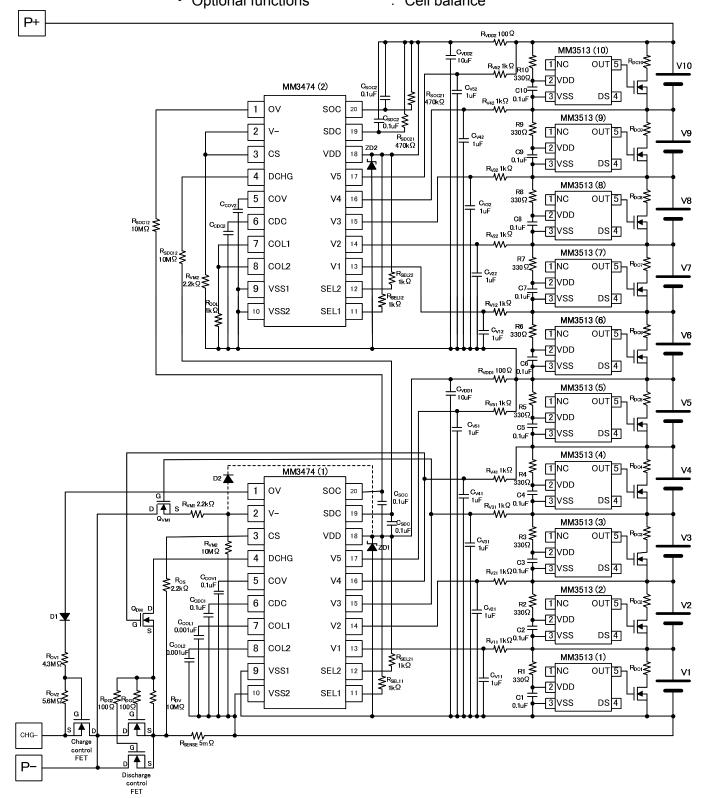


15-2. Examples of circuit using cell balance MM3513

15-2-2. Circuit condition 2 Circuit condition 2

Number of cells10cells (5cells + 5cells)

Charge and discharge route : Separated
 Overdischarge release metho : Voltage release
 Optional functions : Cell balance



# 16. Line up list of related products

16-1. MM3220V serise product lineup

	Det	ection / Re	elease vol	tage	delay	/ time	
Product name (MM3220)	Overcharge detection voltage	Overcharge release voltage	Overdischarge detection voltage	Overdescharge release voltage	Overcharge detection delay time	Overdischarge detection delay time	MM3474□□□VBE Correspondence rank
	V	V	V	V	sec	sec	
V01NRH	4.250	4.150	2.800	3.000	1.0	1.0	C01/C03/C04/C05/E01/E04/E05
V02NRH	3.850	3.650	2.300	2.500	1.0	1.0	D01
V05NRH	4.250	4.150	2.500	3.000	1.0	1.0	F01/F03/F05
V06NRH	4.200	4.100	2.750	3.000	1.0	1.0	G01/G03
V07NRH	4.250	4.150	2.750	3.000	1.0	1.0	G02/G05/G07
V12NRH	3.750	3.550	2.200	2.700	1.0	1.0	L02/L04
V14NRH	3.900	3.600	2.000	3.000	1.0	1.0	N01
V15NRH	4.200	4.100	2.500	3.000	1.0	1.0	F02
V23NRH	4.200	4.170	2.750	2.800	1.0	1.0	P04

Please inquire to us, if you request a rank other than the above.

# 16. Line up list of related products

16-2. MM3513 serise product lineup

Product name (MM3513)	< Detection voltage	Hysteresis voltage	Detection delay time	Release delay time
A01NRH	4.150	0.010	sec 0.25	ms 8.0
B01NRH	3.750	0.010	0.25	8.0
C01NRH	4.200	0.010	0.25	8.0
D01NRH	3.600	0.010	0.25	8.0
D02NRH	3.600	0.100	0.25	8.0
F01NRH	3.650	0.010	0.25	8.0
H01NRH	4.175	0.010	0.25	8.0
J01NRH	3.475	0.010	0.25	8.0
K01NRH	4.180	0.010	0.25	4000.0
L01NRH	4.175	0.000	0.25	4000.0
R01NRH	4.210	0.010	0.25	8.0

Please inquire to us, if you request a rank other than the above.

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Please handle with care since the pins of this product may be subject to damage of electrostatic.

#### 18. Related materials

Lithium-ion battery 3 to 5 cells protection IC Lithium-ion battery 2 cells protection IC Cell balance control IC MM3474 data sheet MM3220 data sheet MM3513 data sheet

\*The contents mentioned in this application note and data sheets are changed without notice.

Please contact to our sales department for the latest edition.